High Efficiency, Main Power Supply Controllers for Notebook Computers

General Description

The RT8205A/B/C dual step-down, switch-mode power-supply controller generates logic-supply voltages in battery-powered systems. The RT8205A/B/C includes two pulse-width modulation (PWM) controllers fixed at 5V/3.3V or adjustable from 2V to 5.5V. An alternative LGATE1 output LG1_CP can be used for external charge pump (RT8205B). And an optional external charge pump can be monitored through SECFB (RT8205C). This device also features 2 linear regulators providing fixed 5V and 3.3V outputs. The linear regulator each provides up to 70mA output current with automatic linear-regulator bootstrapping to the PWM outputs. The RT8205A/B/C includes on-board power-up sequencing, the power-good output, internal soft-start, and internal soft-discharge output that prevents negative voltages on shutdown.

A constant on-time PWM control scheme operates without sense resistor and provides 100ns response to load transients while maintaining a relatively constant switching frequency. The unique ultrasonic mode maintains the switching frequency above 25kHz, which eliminates noise in audio applications. Other features include diode-emulation mode (DEM), which maximizes efficiency in light-load applications, and fixed-frequency PWM mode, which reduces RF interference in sensitive application

Features

- **Wide Input Voltage Range 6V to 25V**
- **Dual Fixed 5V/3.3V Outputs or Adjustable from 2V to 5.5V, 1.5% Accuracy.**
- **Alternative LGATE1 Output (LG1_CP) acts as Clock for Charge Pump (RT8205B)**
- **Secondary Feedback Input Maintains Charge Pump Voltage (RT8205C)**
- **Fixed 3.3V and 5V LDO Output : 70mA**
- **2V Reference Voltage ±1% : 50μA**
- **Constant ON-Time Control with 100ns Load Step Response**
- **Frequency Selectable via TONSEL Setting**
- **$R_{DS(ON)}$ Current Sensing and Programmable Current Limit combined with Enable Control**
- **Selectable PWM, DEM, or Ultrasonic Mode**
- **Internal Soft-Start and Soft-Discharge**
- **High Efficiency up to 97%**
- **5mW Quiescent Power Dissipation**
- **Thermal Shutdown**
- **RoHS Compliant and Halogen Free**

Applications

- Notebook and Sub-Notebook Computers
- 3-Cell and 4-Cell Li+ Battery-Powered Devices

Ordering Information

RT8205□□□

- Package Type
  QW : WQFN-24L 4x4 (W-Type)
- Lead Plating System
  G : Green (Halogen Free and Pb Free)
- Pin Function
  A : Default
  B : With LG1_CP
  C : With SECFB

Note :

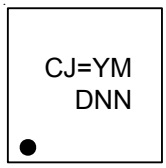
Richtek products are :

- RoHS compliant and compatible with the current requirements of IPC/JEDEC J-STD-020.
- Suitable for use in SnPb or Pb-free soldering processes.

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Marking Information

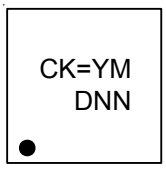
RT8205AGQW



CJ= : Product Code

YMDNN : Date Code

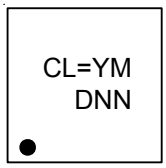
RT8205BGQW



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RT8205CGQW

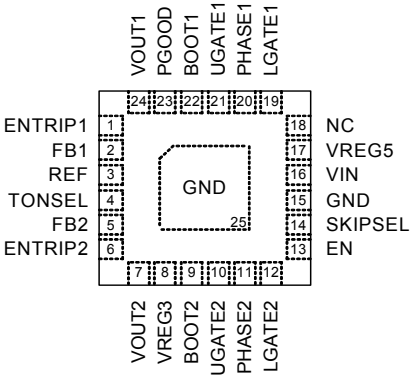


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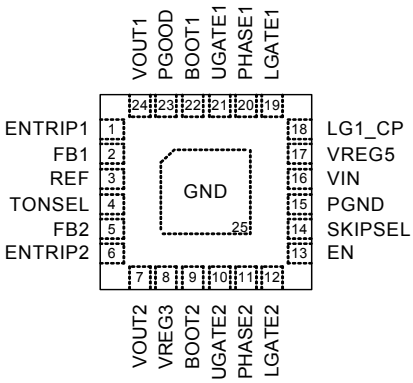
Pin Configurations

(TOP VIEW)



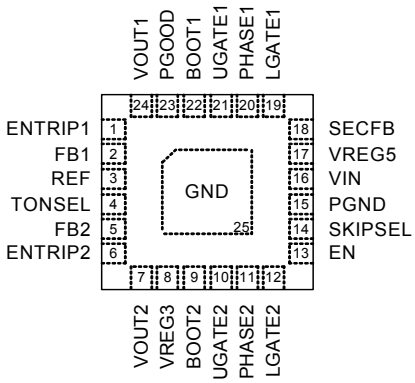
RT8205A

WQFN-24L 4x4



RT8205B

WQFN-24L 4x4

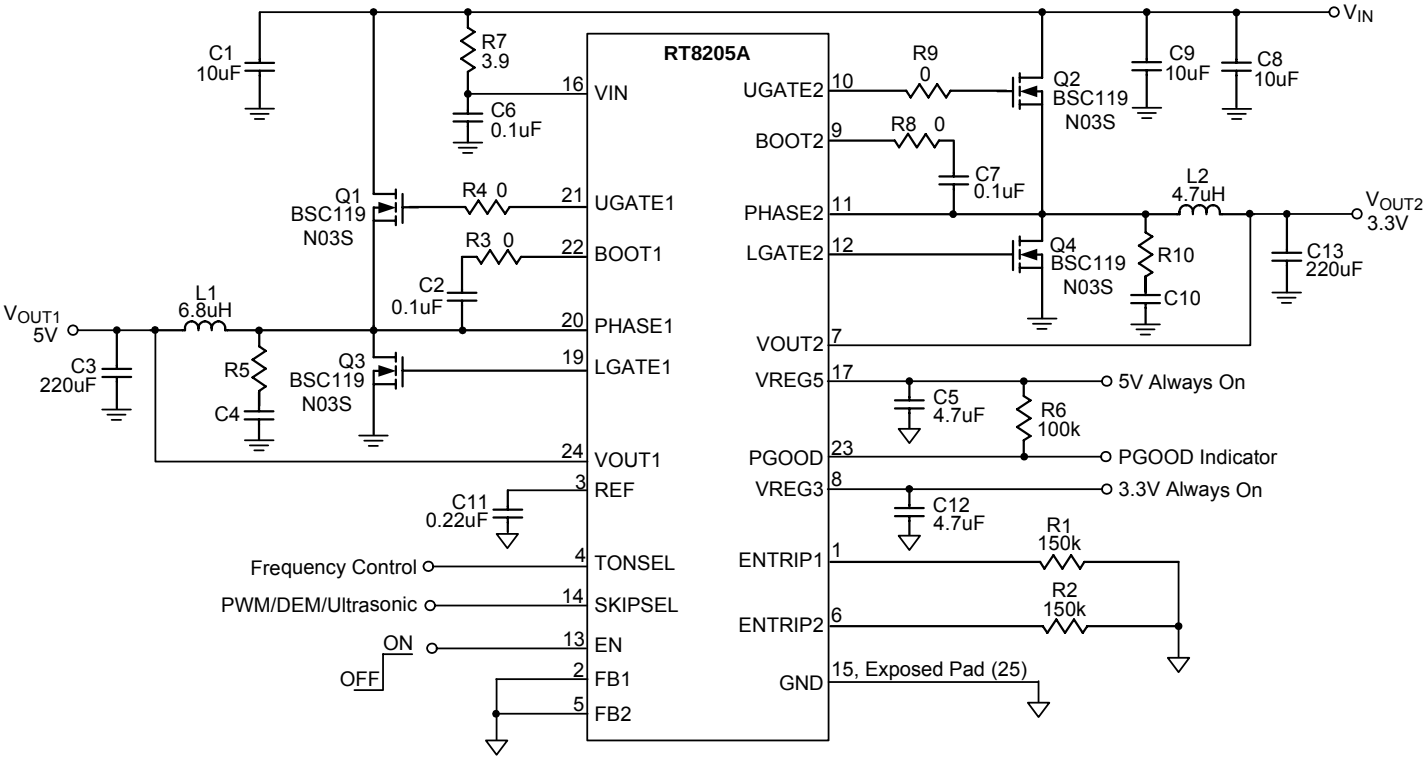


RT8205C

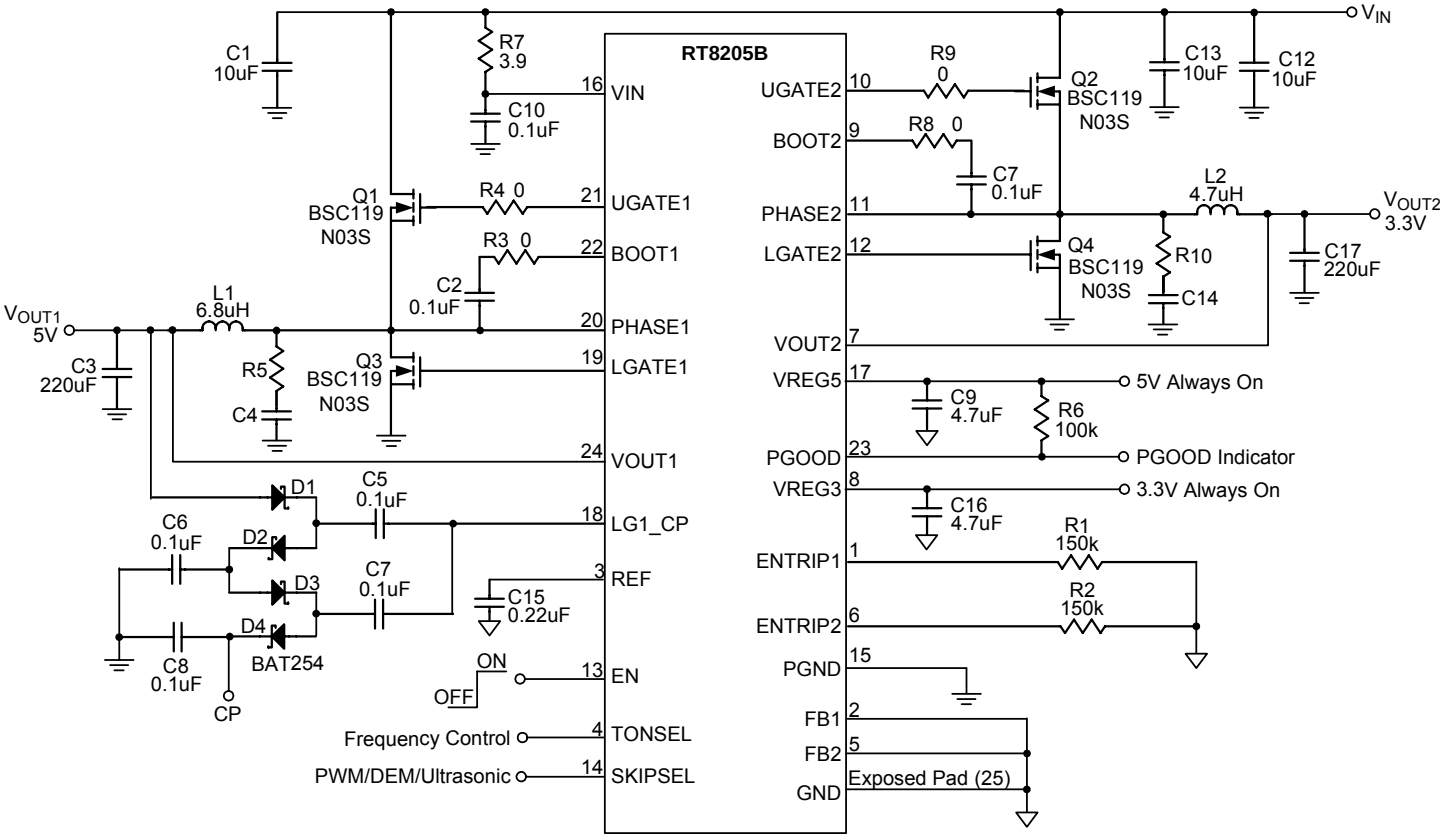
WQFN-24L 4x4

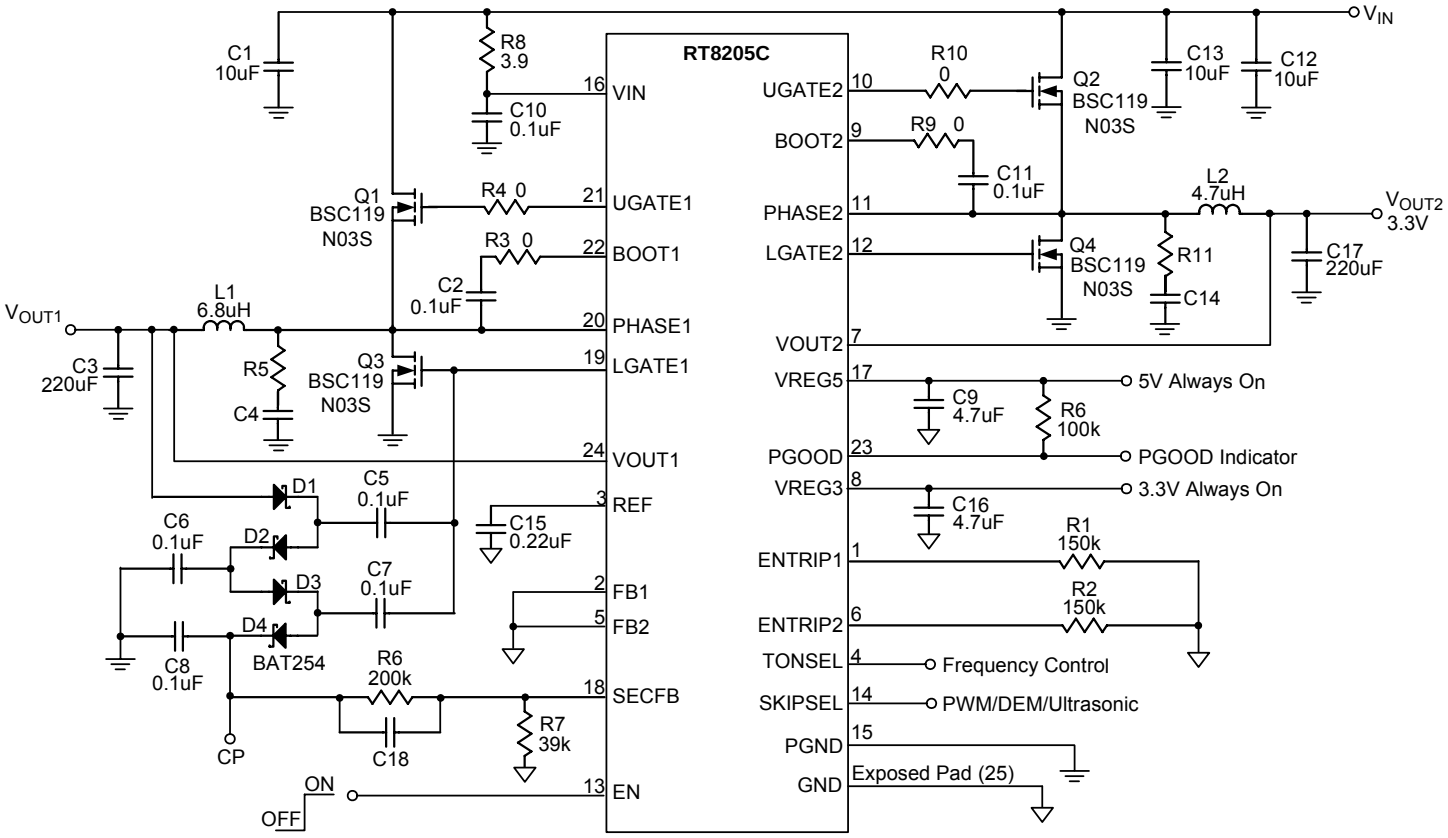
Typical Application Circuit

For Fixed Voltage Regulator



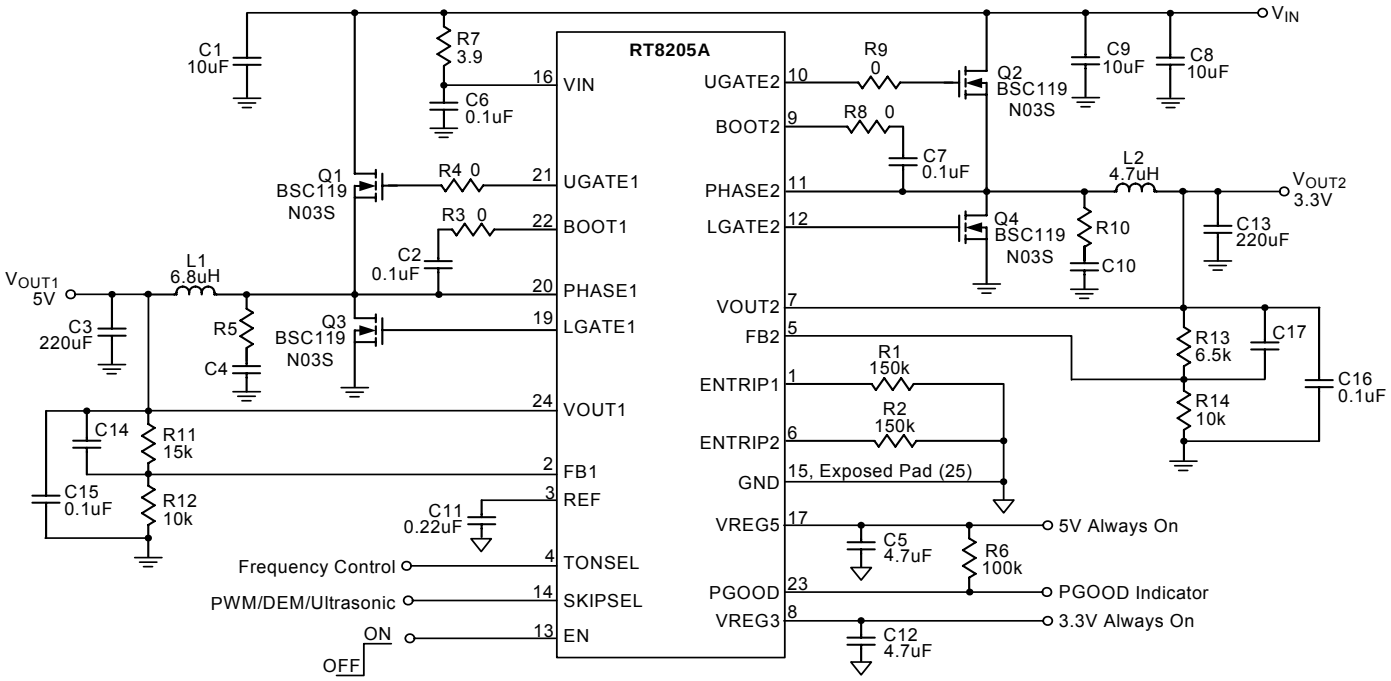
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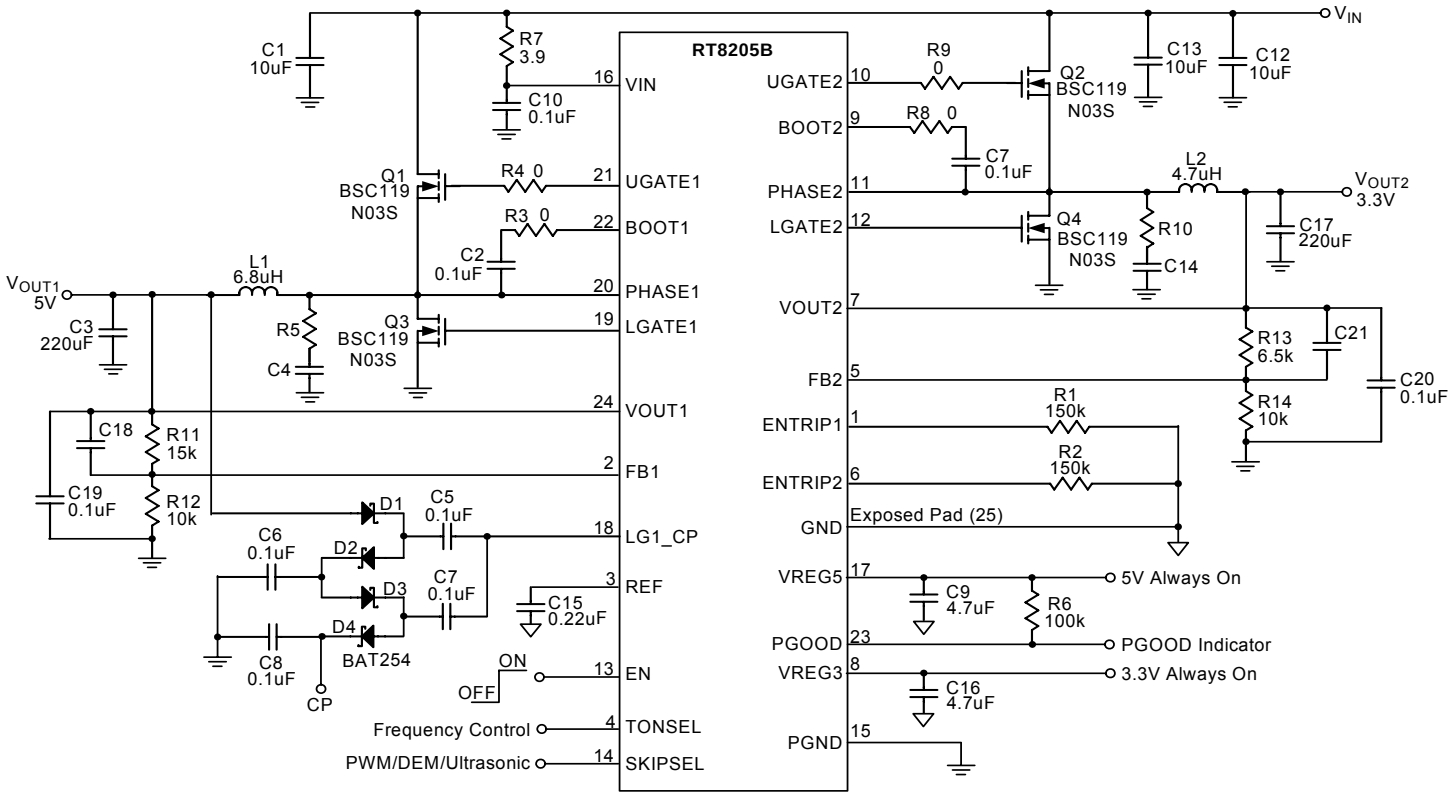




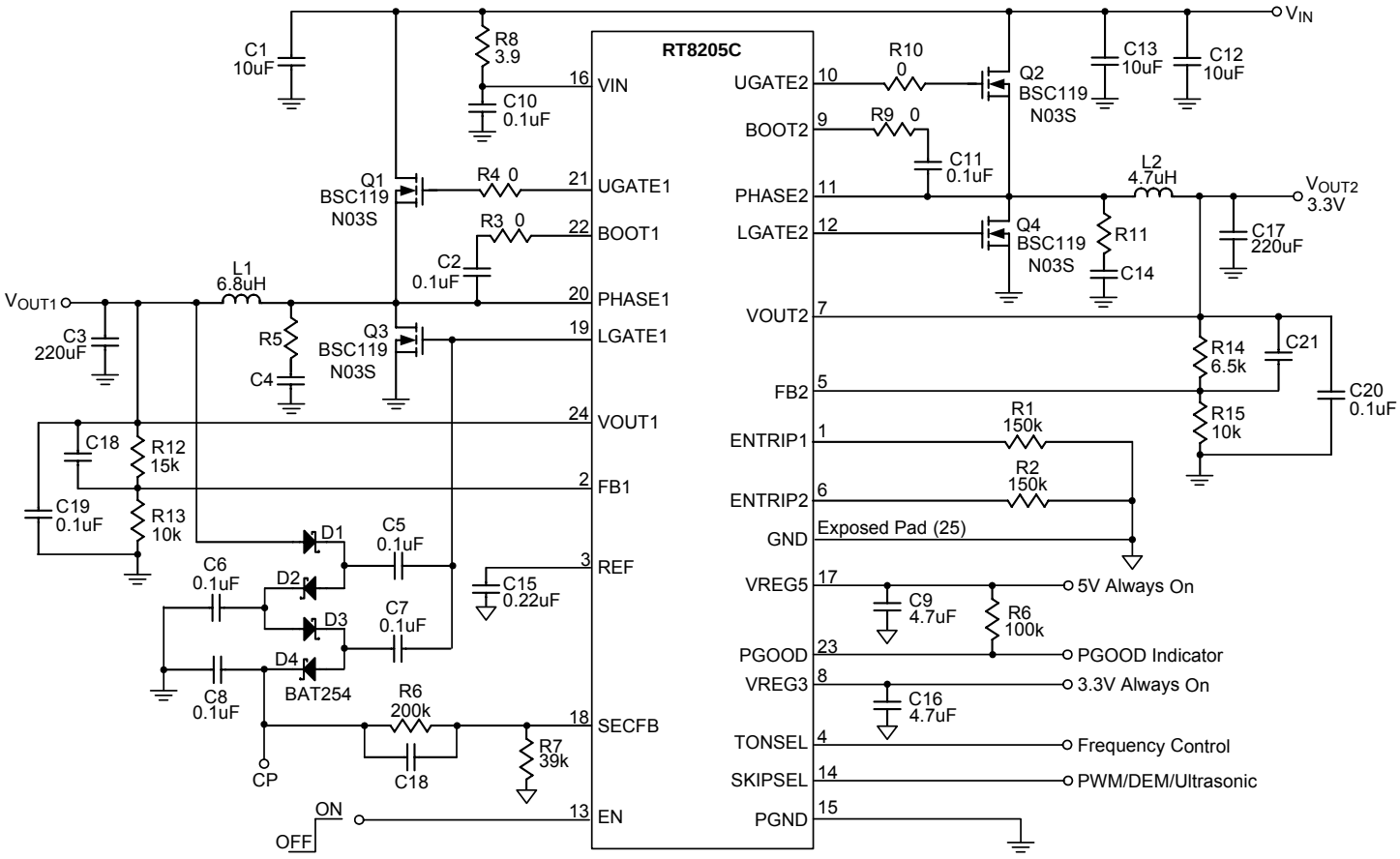
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For Adjustable Voltage Regulator



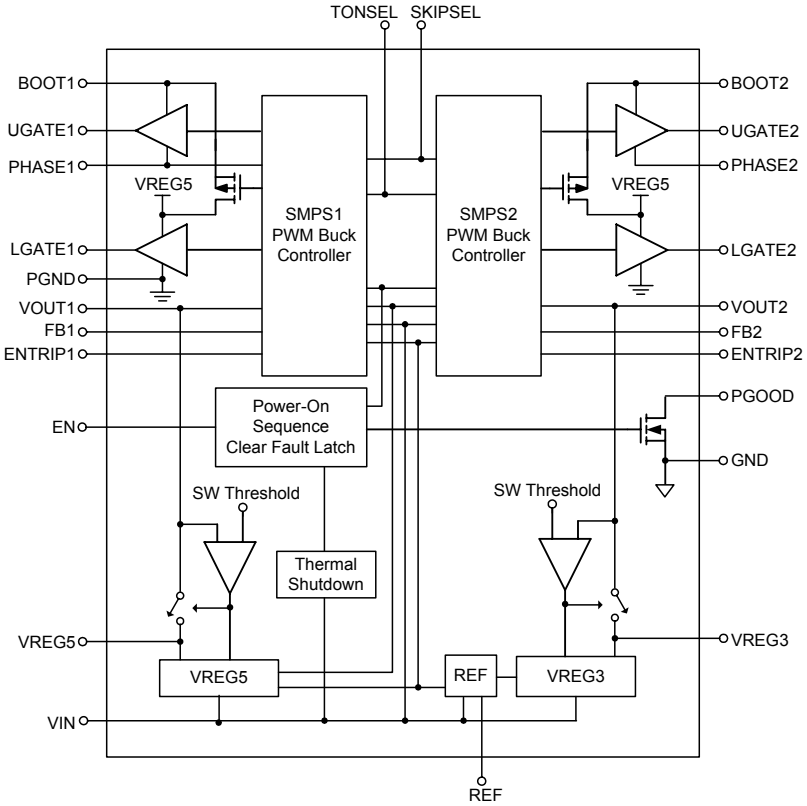


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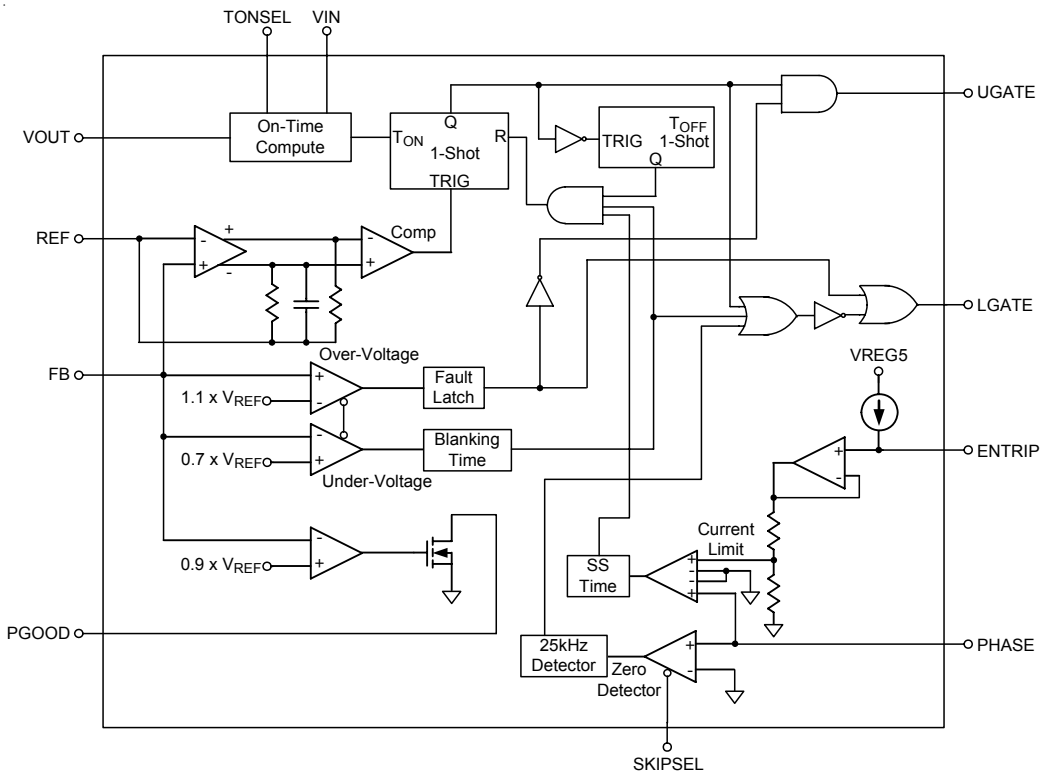


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Function Block Diagram



Function Block Diagram



PWM Controller (One Side)

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Functional Pin Description

ENTRIP1 (Pin 1)

Channel 1 enable and Current Limit setting Input. Connect resistor to GND to set the threshold for channel 1 synchronous $R_{DS(ON)}$ sense. The GND-PHASE1 current-limit threshold is 1/10th the voltage seen at ENTRIP1 over a 0.5V to 2V range. There is an internal 10uA current source from VREG5 to ENTRIP1. The logic current limit threshold is default to 200mV value if ENTRIP1 is higher than VREG5-1V.

FB1 (Pin 2)

SMPS1 Feedback Input. Connect FB1 to VREG5 or GND for fixed 5V operation. Or connect FB1 to a resistive voltage-divider from VOUT1 to GND to adjust output from 2V to 5.5V.

REF (Pin 3)

2V Reference Output. Bypass to GND with a 0.22uF capacitor. REF can source up to 50uA for external loads. Loading REF degrades FBx and output accuracy according to the REF load-regulation error.

TONSEL (Pin 4)

Frequency Selectable Input for VOUT1/VOUT2 respectively.

400kHz/500kHz : Connect to VREG5 or VREG3

300kHz/375kHz : Connect to REF

200kHz/250kHz : Connect to GND

FB2 (Pin 5)

SMPS2 Feedback Input. Connect FB2 to VREG5 or GND for fixed 3.3V operation. Or connect FB2 to a resistive voltage-divider from VOUT2 to GND to adjust output from 2V to 5.5V.

ENTRIP2 (Pin 6)

Channel 2 enable and Current Limit setting Input. Connect resistor to GND to set the threshold for channel 2 synchronous $R_{DS(ON)}$ sense. The GND-PHASE2 current-limit threshold is 1/10th the voltage seen at ENTRIP2 over a 0.5V to 2V range. There is an internal 10uA current source from VREG5 to ENTRIP2. The logic current limit threshold is default to 200mV value if ENTRIP2 is higher than VREG5-1V.

VOUT2 (Pin 7)

SMPS2 Output Voltage-Sense Input. Connect to the SMPS2 output. VOUT2 is an input to the on-time one-shot circuit. It also serves as the SMPS2 feedback input in fixed-voltage mode.

VREG3 (Pin 8)

3.3V Linear Regulator Output.

BOOT2 (Pin 9)

Boost Flying Capacitor Connection for SMPS2. Connect to an external capacitor according to the typical application circuits.

UGATE2 (Pin 10)

High-Side MOSFET Floating Gate-Driver Output for SMPS2. UGATE2 swings between PHASE2 and BOOT2.

PHASE2 (Pin 11)

Inductor Connection for SMPS2. PHASE2 is the internal lower supply rail for the UGATE2 high-side gate driver. PHASE2 is also the current-sense input for the SMPS2.

LGATE2 (Pin 12)

SMPS2 Synchronous-Rectifier Gate-Drive Output. LGATE2 swings between GND and VREG5.

EN (Pin 13)

Master Enable Input. The REF/VREG5/VREG3 are enabled if it is within logic high level and disable if it is less than the logic low level.

SKIPSEL (Pin 14)

Operation Mode Selectable Input.

Ultrasonic Mode : Connect to VREG5 or VREG3

Diode Emulation Mode : Connect to REF

PWM Mode : Connect to GND

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GND [Pin 15 (RT8205A), Exposed Pad (25)]

Analog Ground for SMPS controller. The exposed pad must be soldered to a large PCB and connected to GND for maximum power dissipation.

PGND (Pin 15) (RT8205B/C)

Power Ground for SMPS controller. Connect PGND externally to the underside of the exposed pad.

VIN (Pin 16)

High Voltage Power Supply Input for 5V/3.3V LDO and Feed-forward ON-Time circuitry.

VREG5 (Pin 17)

5V Linear Regulator Output.VREG5 is also the supply voltage for the low-side MOSFET driver and analog supply voltage for the device.

NC (Pin 18) (RT8205A)

No Internal Connection.

LG1_CP (Pin 18) (RT8205B)

Alternative LGATE1 Output for 14V charge pump.

SECFB (Pin 18) (RT8205C)

The SECFB is used to monitor the optional external 14V charge pump. Connect a resistive voltage-divider from 14V charge pump output to GND to detect the output. If SECFB drops below the threshold voltage, LGATE1 turns on for 300ns (typ.). This will refresh the external charge pump driven by LGATE1 without over-discharging the output voltage.

LGATE1 (Pin 19)

SMPS1 Synchronous-Rectifier Gate-Drive Output. LGATE1 swings between GND and VREG5.

PHASE1 (Pin 20)

Inductor Connection for SMPS1. PHASE1 is the internal lower supply rail for the UGATE1 high-side gate driver. PHASE1 is also the current-sense input for the SMPS1.

UGATE1 (Pin 21)

High-Side MOSFET Floating Gate-Driver Output for SMPS1. UGATE1 swings between PHASE1 and BOOT1.

BOOT1 (Pin 22)

Boost Flying Capacitor Connection for SMPS1. Connect to an external capacitor according to the typical application circuits.

PGOOD (Pin 23)

Power Good Output for channel 1 and channel 2. (Logical AND)

VOUT1 (Pin 24)

SMPS1 Output Voltage-Sense Input. Connect to the SMPS1 output. VOUT1 is an input to the on-time one-shot circuit. It also serves as the SMPS1 feedback input in fixed-voltage mode.

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Absolute Maximum Ratings (Note 1)

- VIN, EN to GND ---------- –0.3V to 28V
- PHASEx to GND
  - DC ---------- –0.3V to 28V
  - < 20ns ---------- –8V
- BOOTx to PHASEx ---------- –0.3V to 6V
- ENTRIPx, SKIPSEL, TONSEL, PGOOD, to GND ---------- –0.3V to 6V
- VREG5, VREG3, FBx, VOUTx, SECFB, REF to GND ---------- –0.3V to (VREG5 + 0.3V)
- UGATEx to PHASEx
  - DC ---------- –0.3V to (VREG5 + 0.3V)
  - < 20ns ---------- –5V
- LGATEx to GND
  - DC ---------- –0.3V to (VREG5 + 0.3V)
  - < 20ns ---------- –2.5V
- Power Dissipation, P_D @ T_A = 25°C
  - WQFN-24L 4x4 ---------- 1.923W
- Package Thermal Resistance (Note 2)
  - WQFN-24L 4x4, θ_{JA} ---------- 52°C/W
  - WQFN-24L 4x4, θ_{JC} ---------- 7°C/W
- Lead Temperature (Soldering, 10 sec.) ---------- 260°C
- Junction Temperature ---------- 150°C
- Storage Temperature Range ---------- –65°C to 150°C
- ESD Susceptibility (Note 3)
  - HBM (Human Body Model) ---------- 2kV

Recommended Operating Conditions (Note 4)

- Input Voltage, VIN ---------- 6V to 25V
- Junction Temperature Range ---------- –40°C to 125°C
- Ambient Temperature Range ---------- –40°C to 85°C

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To be continued

Electrical Characteristics

(V_{IN} = 12V, EN = 5V, ENTRIP1 = ENTRIP2 = 2V, No Load on VREG5, VREG3, VOUT1, VOUT2 and REF, T_A = 25°C, unless otherwise specified)

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Input Supply							
VIN Standby Supply Current	I_{VIN_SBY}	V_{IN} = 6V to 25V, Both SMPS Off, EN = 5V		--	200	--	μA
VIN Shutdown Supply Current	I_{VIN_SHDH}	V_{IN} = 6V to 25V, ENTRIPx = EN = GND		--	20	40	μA
Quiescent Power Consumption		Both SMPSs On, FBx = SKIPSEL = REF V_{OUT1} = 5.3V, V_{OUT2} = 3.5V (Note 5)		--	5	7	mW
SMPS Output and FB Voltage							
VOUT1 Output Voltage in Fixed Mode	V_{OUT1}	V_{IN} = 6V to 25V, FB1= GND or 5V, SKIPSEL = GND		4.975	5.05	5.125	V
VOUT2 Output Voltage in Fixed Mode	V_{OUT2}	V_{IN} = 6V to 25V, FB2 = GND or 5V, SKIPSEL = GND		3.285	3.33	3.375	V
FBx in Output Adjustable Mode	FBx	V_{IN} = 6V to 25V		1.975	2	2.025	V
SECFB Voltage	SECFB	V_{IN} = 6V to 25V (RT8205C)		1.92	2	2.08	V
Output Voltage Adjust Range	V_{OUTx}	SMPS1, SMPS2		2	--	5.5	V
FBx Adjustable-mode Threshold Voltage		Fixed or Adj-Mode comparator threshold		0.2	0.4	0.55	V
DC Load Regulation	V_{LOAD}	Either SMPS, SKIPSEL = GND, 0 to 5A		--	−0.1	--	%
		Either SMPS, SKIPSEL = VREG5, 0 to 5A		--	−1.7	--	%
		Either SMPS, SKIPSEL = REF, 0 to 5A		--	−1.5	--	%
Line Regulation	V_{LINE}	Either SMPS, V_{IN} = 6V to 25V		--	0.005	--	%/V
On Time							
On-Time Pulse Width	t_{UGATEx}	TONSEL = GND	V_{OUT1} = 5.05V	1895	2105	2315	ns
			V_{OUT2} = 3.33V	999	1110	1221	
		TONSEL = REF	V_{OUT1} = 5.05V	1227	1403	1579	
			V_{OUT2} = 3.33V	647	740	833	
		TONSEL = VREG5	V_{OUT1} = 5.05V	895	1052	1209	
			V_{OUT2} = 3.33V	475	555	635	
Minimum Off-Time	t_{LGATEx}			200	300	400	ns
Ultrasonic Mode Frequency		SKIPSEL = VREG5 or VREG3		25	33	--	kHz
Soft Start							
Soft-Start Time	t_{SSx}	Zero to Full Limit from ENTRIPx Enable		--	2	--	ms
Current Sense							
Current Limit Threshold (Default)		$V_{ENTRIPx}$ = VREG5, GND−PHASEx		180	200	220	mV
ENTRIPx Source Current	$I_{ENTRIPx}$	$V_{ENTRIPx}$ = 0.9V		9.4	10	10.6	μA
ENTRIPx Current Temperature Coefficient	$TC_{IENTRIPx}$			--	1600	--	PPM/°C
ENTRIPx Adjustment Range		$V_{ENTRIPx}$ = $I_{ENTRIPx}$ x $R_{ENTRIPx}$		0.5	--	2	V

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Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Current-Limit Threshold		GND–PHASEx	$V_{ENTRIPx}$ = 0.5V	40	50	60	mV
			$V_{ENTRIPx}$ =1V	90	100	110	mV
			$V_{ENTRIPx}$ =2V	180	200	220	mV
Zero-Current Threshold		SKIPSEL = VREG5 or REF, GND–PHASEx		--	3	--	mV
Internal Regulator and Reference							
VREG5 Output Voltage	V_{VREG5}	V_{OUT1} = GND, 6V < V_{IN} < 25V, 0 < I_{VREG5} < 70mA		4.8	5	5.2	V
VREG3 Output Voltage	V_{VREG3}	V_{OUT2} = GND, 6V < V_{IN} < 25V, 0 < I_{VREG3} < 70mA		3.2	3.33	3.46	V
VREG5 Short Current	I_{VREG5}	VREG5 = GND, V_{OUT1} = GND		--	175	275	mA
VREG3 Short Current	I_{VREG3}	VREG3 = GND, V_{OUT2} = GND		--	175	275	mA
VREG5 Switchover Threshold to V_{OUT1}		Rising Edge at V_{OUT1} Regulation Point		4.53	4.66	4.79	V
VREG3 Switchover Threshold to V_{OUT2}		Rising Edge at V_{OUT2} Regulation Point		2.96	3.06	3.16	V
VREGx Switchover Equivalent Resistance	R_{SW}	VREGx to V_{OUTx}, 10mA		--	1.5	3	Ω
REF Output Voltage	V_{REF}	No External Load		1.98	2	2.02	V
REF Load Regulation		0 < I_{LOAD} < 50uA		--	10	--	mV
REF Sink Current		REF in Regulation		5	--	--	μA
UVLO							
VREG3 UVLO Threshold		SMPSx off		--	2.5	--	V
VREG5 UVLO Threshold		Rising Edge		--	4.35	4.5	V
		Falling Edge		3.9	4.05	4.25	V
Power Good							
PGOOD Threshold		FBx with Respect to Internal Reference, Falling Edge, Hysteresis = 1%		–11	–7.5	–4	%
PGOOD Propagation Delay		Falling Edge, 50mV Overdrive		--	10	--	μs
PGOOD Leakage Current		High State, Forced to 5.5V		--	--	1	μA
PGOOD Output Low Voltage		I_{SINK} = 4mA		--	--	0.3	V
Fault Detection							
OVP Trip Threshold	V_{FB_OVP}	FBx with Respect to Internal Reference		108	111	115	%
OVP Propagation Delay				--	10	--	μs
UVP Trip Threshold		FBx with Respect to Internal Reference		65	70	75	%
UVP Shutdown Blanking Time	t_{SHDN_UVP}	From ENTRIPx Enable		--	3	--	ms
Thermal Shutdown							
Thermal Shutdown	T_{SHDN}			--	150	--	°C
Thermal Shutdown Hysteresis				--	10	--	°C

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Parameter		Symbol	Test Conditions	Min	Typ	Max	Unit
VOUT Discharge							
VOUTx Discharge Current		I_{DISx}	ENTRIPx = GND, V_{OUTx} = 0.5V	10	60	--	mA
Logic Input							
FB1/FB2 Input Voltage			Low Level (Internal Fixed VOUTx)	--	--	0.2	V
			High Level (Internal Fixed VOUTx)	4.5	--	--	V
SKIPSEL Input Voltage			Low Level (PWM Mode)	--	--	0.8	V
			REF Level (DEM Mode)	1.8	--	2.3	V
			High Level (Ultrasonic Mode)	2.5	--	--	V
ENTRIPx Input Voltage			SMPS On Level	0.35	0.4	0.45	V
EN Threshold Voltage	Logic-High	V_{IH}		1	--	--	V
	Logic-Low	V_{IL}		--	--	0.4	
TONSEL Setting Voltage			V_{OUT1}/V_{OUT2} = 200kHz/250kHz	--	--	0.8	V
			V_{OUT1}/V_{OUT2} = 300kHz/375kHz	1.8	--	2.3	
			V_{OUT1}/V_{OUT2} = 400kHz/500kHz	2.5	--	--	
Input Leakage Current			EN = 0V or 25V	–1	--	3	μA
			TONSEL, SKIPSEL = 0V or 5V	–1	--	1	
			FBx = SECFB = 0V or 5V	–1	--	1	
Internal BOOT Switch							
Internal Boost Charging Switch On-Resistance			VREG5 to BOOTx	--	20	--	Ω
Power MOSFET Drivers							
UGATEx Driver Sink/Source Current			UGATEx Forced to 2V	--	2	--	A
LGATEx Driver Source Current			LGATEx Forced to 2V	--	1.7	--	A
LGATEx Driver Sink Current			LGATEx Forced to 2V	--	3.3	--	A
UGATEx On-Resistance			BOOTx to PHASEx Forced to 5V	--	1.5	4	Ω
LGATEx On-Resistance			LGATEx, High State	--	2.2	5	Ω
			LGATEx, Low State	--	0.6	1.5	
Dead Time			LGATEx Rising	--	30	--	ns
			UGATEx Rising	--	40	--	

Note 1. Stresses beyond those listed “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions may affect device reliability.

Note 2. θ_{JA} is measured at T_A = 25°C on a high effective thermal conductivity four-layer test board per JEDEC 51-7. θ_{JC} is measured at the exposed pad of the package.

Note 3. Devices are ESD sensitive. Handling precaution is recommended.

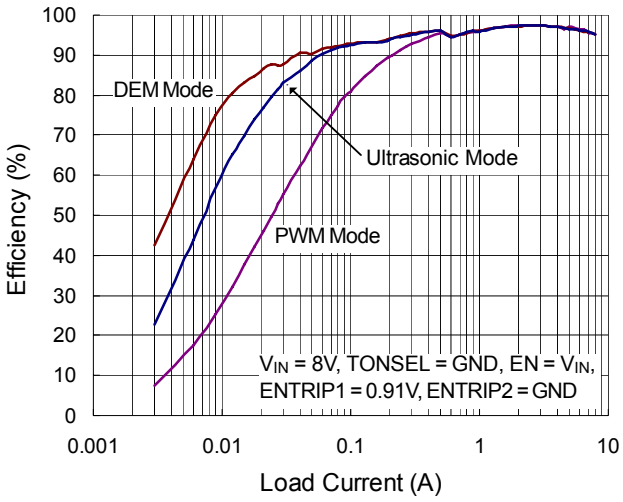
Note 4. The device is not guaranteed to function outside its operating conditions.

Note 5. P_{VIN} + P_{VREG5}

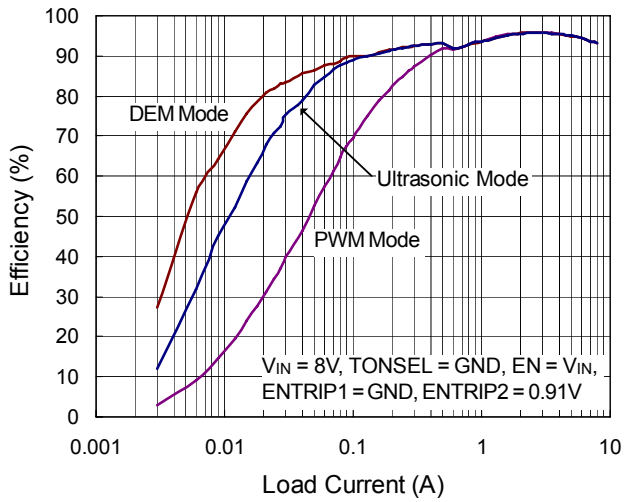
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Typical Operating Characteristics

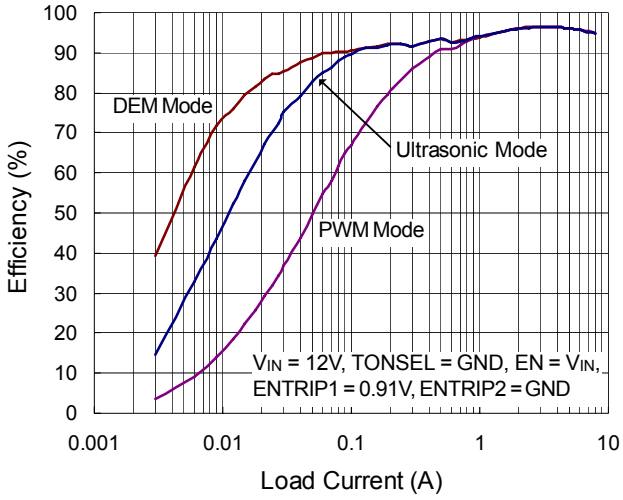
V_{OUT1} Output Efficiency vs. Load Current



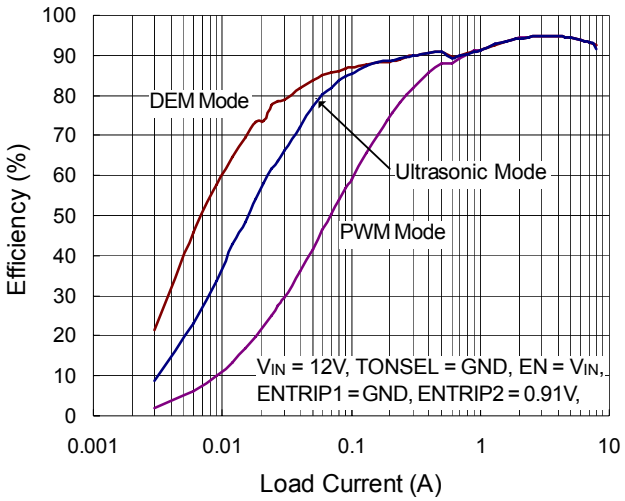
V_{OUT2} Output Efficiency vs. Load Current



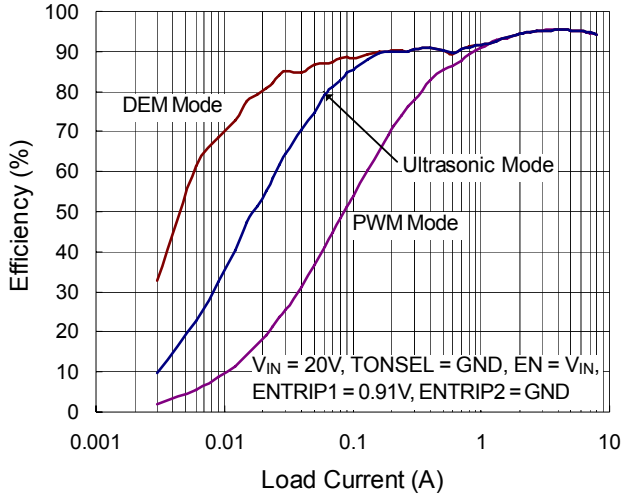
V_{OUT1} Output Efficiency vs. Load Current



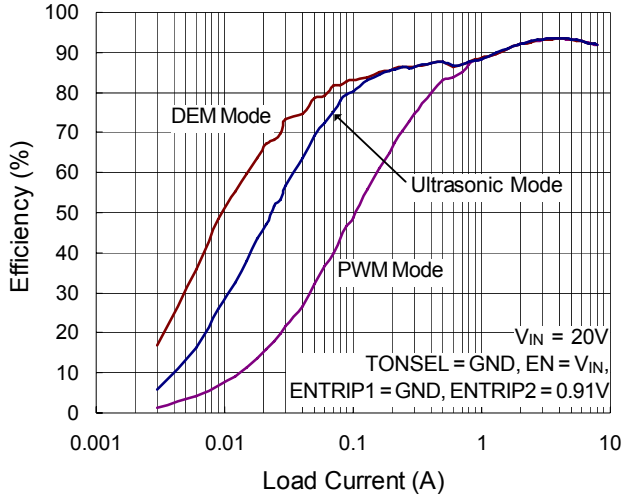
V_{OUT2} Output Efficiency vs. Load Current



V_{OUT1} Output Efficiency vs. Load Current

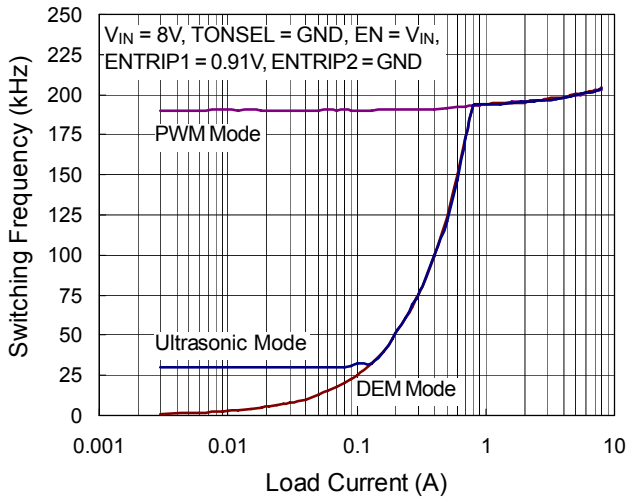


V_{OUT2} Output Efficiency vs. Load Current

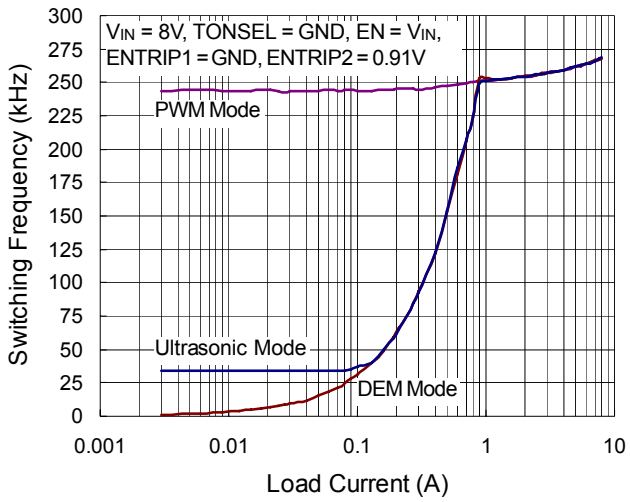


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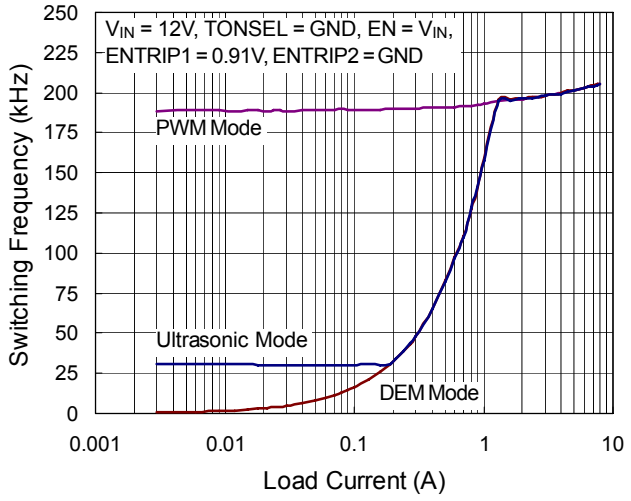
V_{OUT1} Output Switching Frequency vs. Load Current



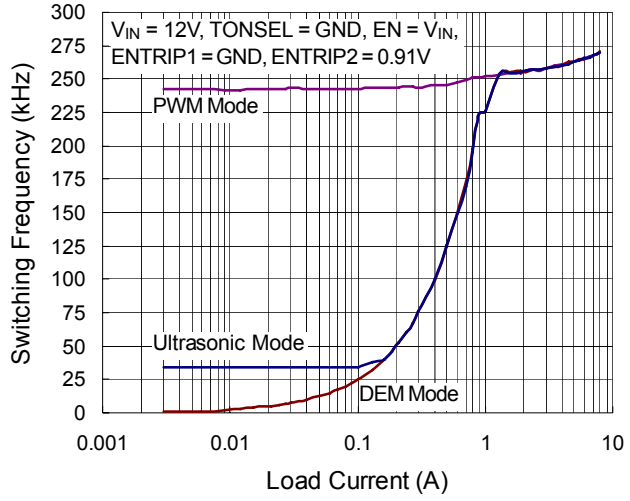
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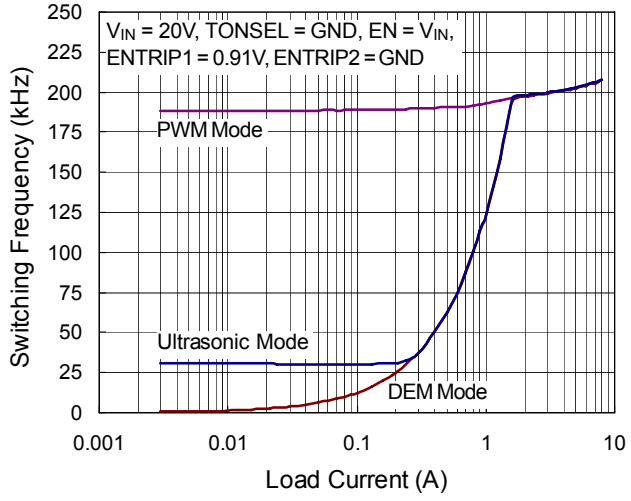
V_{OUT1} Output Switching Frequency vs. Load Current



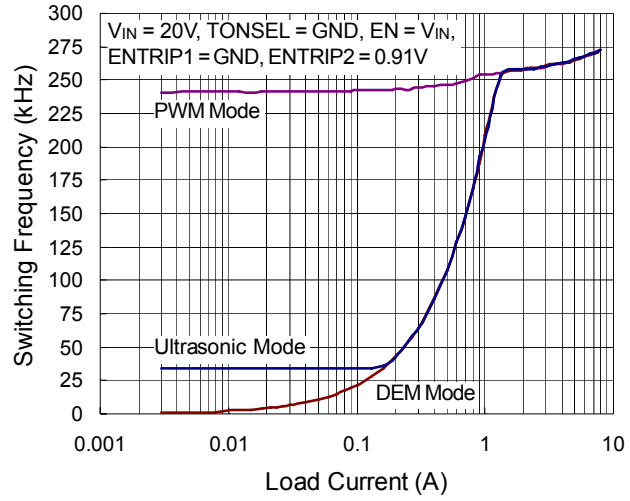
V_{OUT2} Output Switching Frequency vs. Load Current



V_{OUT1} Output Switching Frequency vs. Load Current

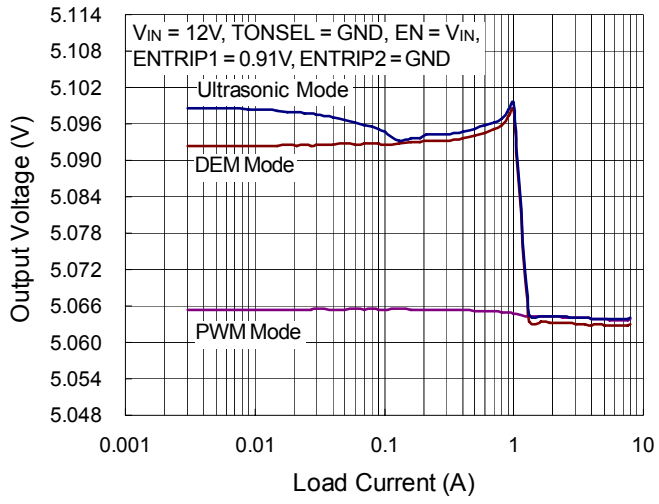


V_{OUT2} Output Switching Frequency vs. Load Current

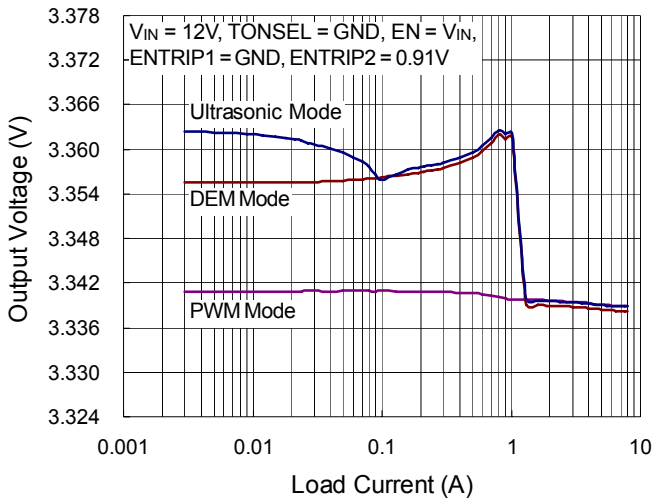


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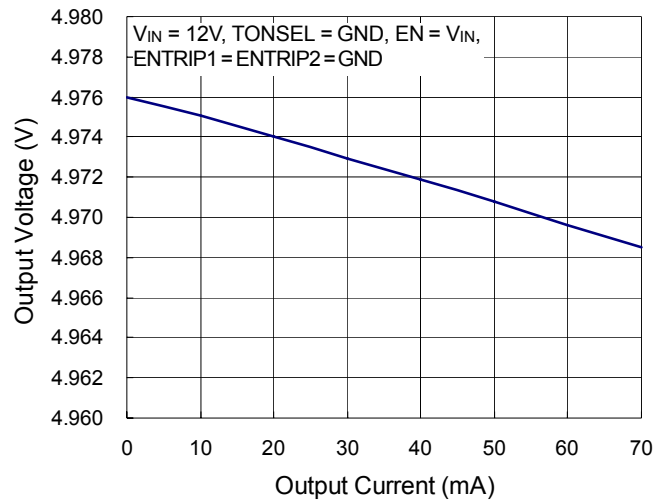
V_{OUT1} Output Voltage vs. Load Current



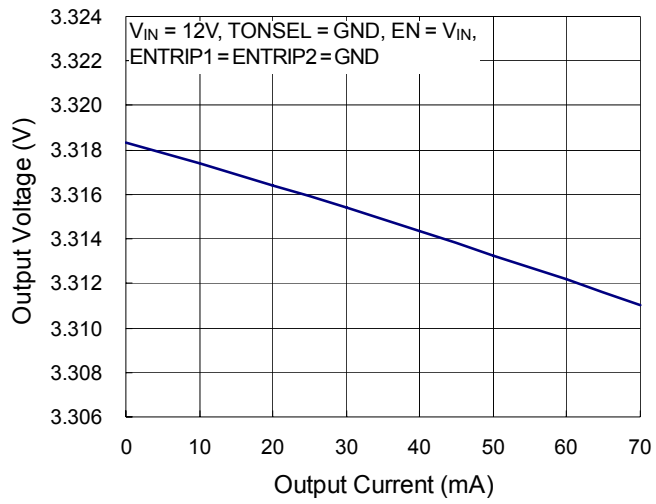
V_{OUT2} Output Voltage vs. Load Current



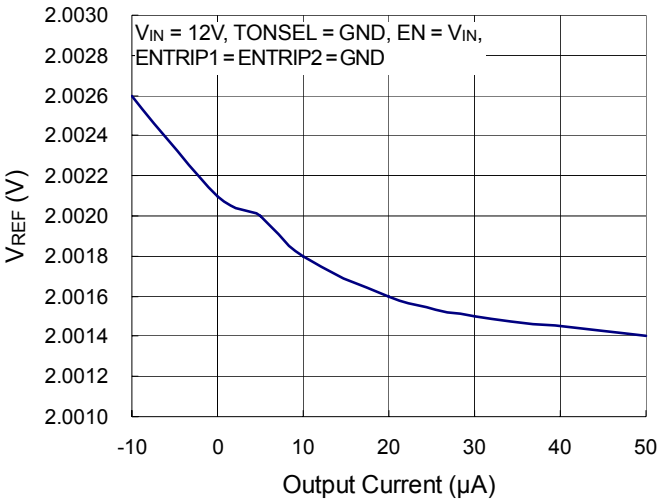
VREG5 Output Voltage vs. Output Current



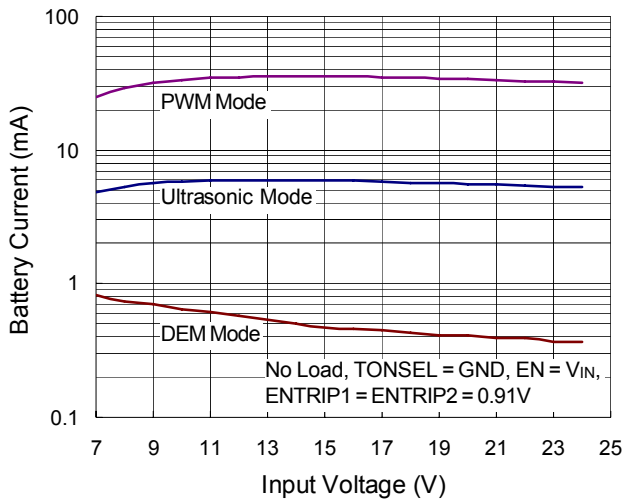
VREG3 Output Voltage vs. Output Current



V_{REF} vs. Output Current

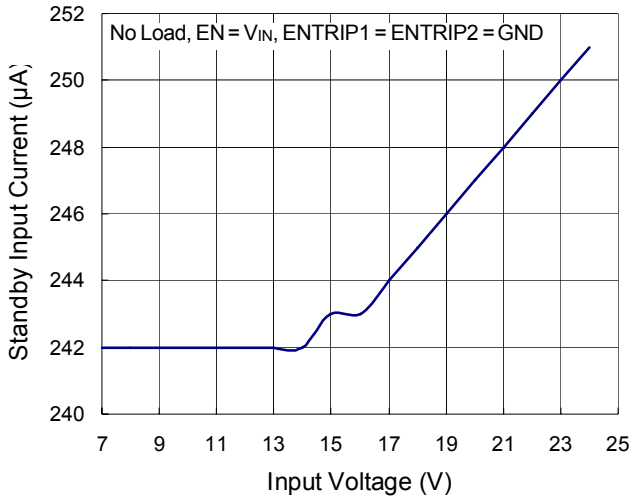


Battery Current vs. Input Voltage

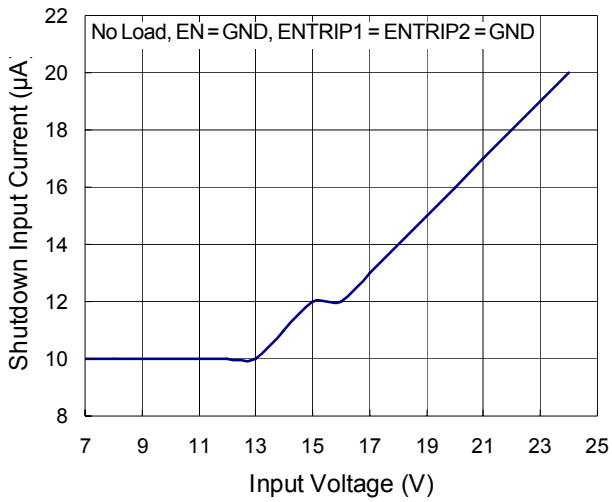


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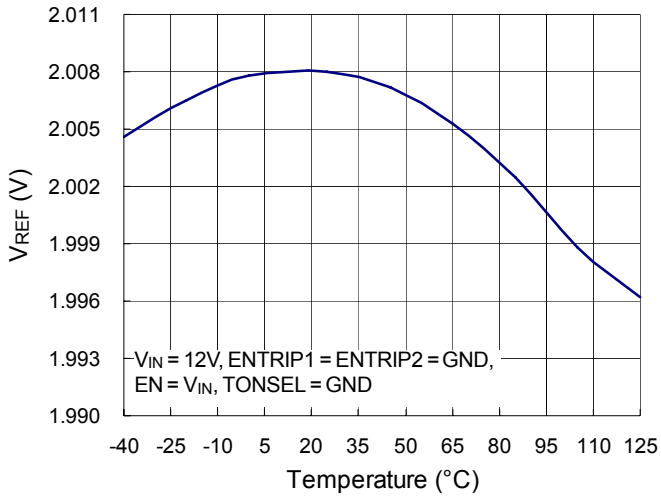
Standby Input Current vs. Input Voltage



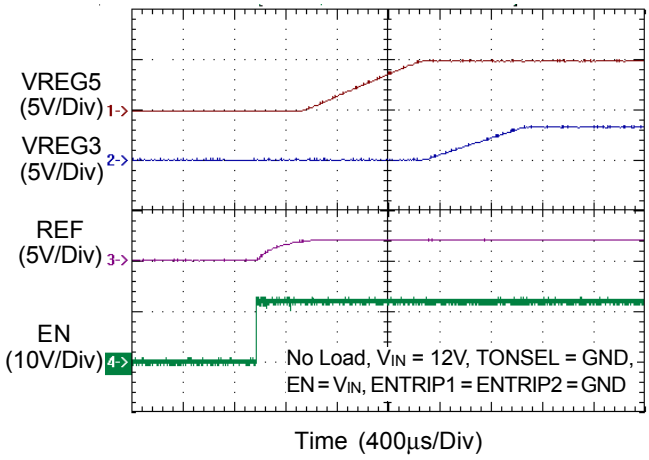
Shutdown Input Current vs. Input Voltage



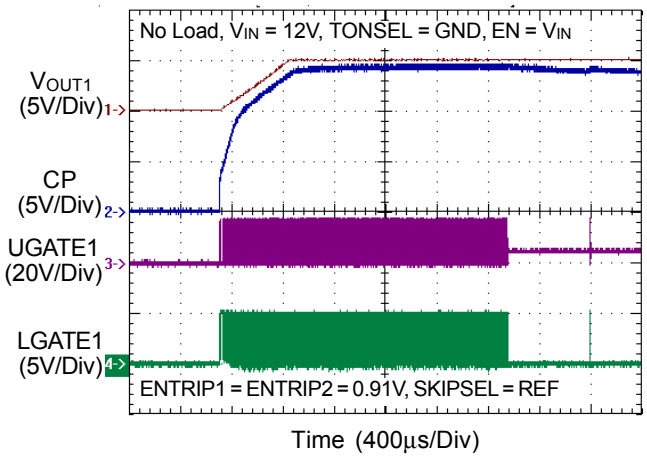
V_{REF} vs. Temperature



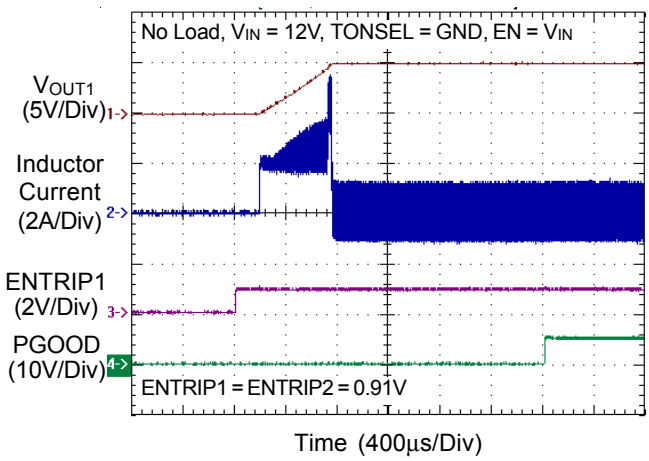
Start Up



CP Start Up

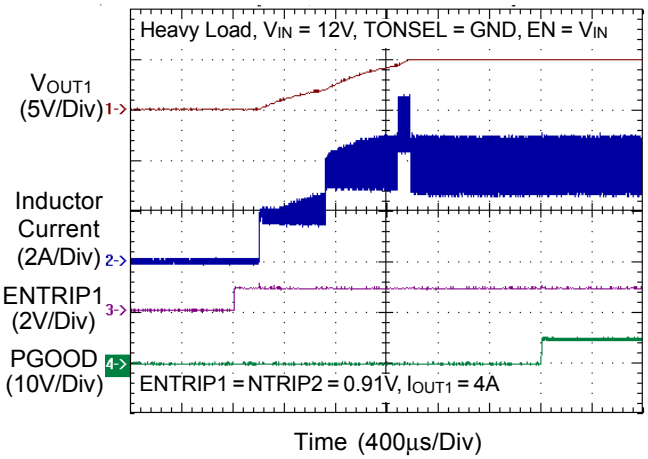


V_{OUT1} Start Up

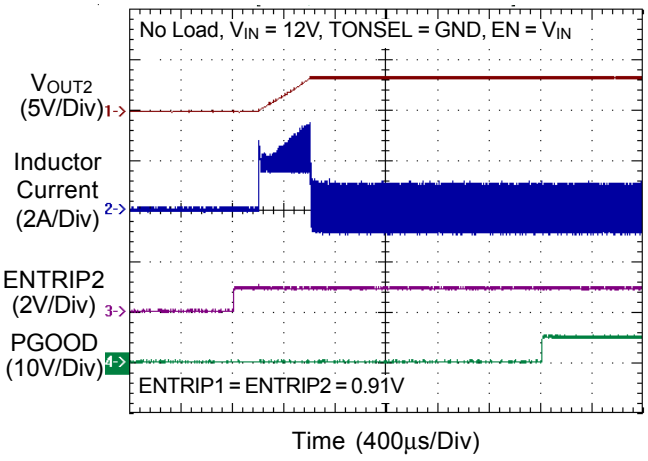


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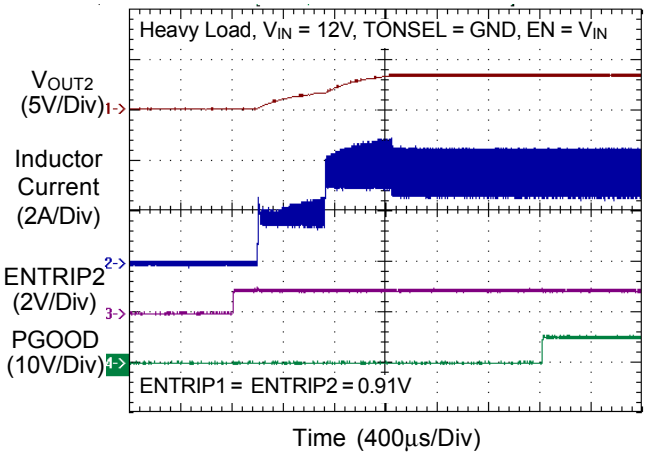
V_{OUT1} Start Up



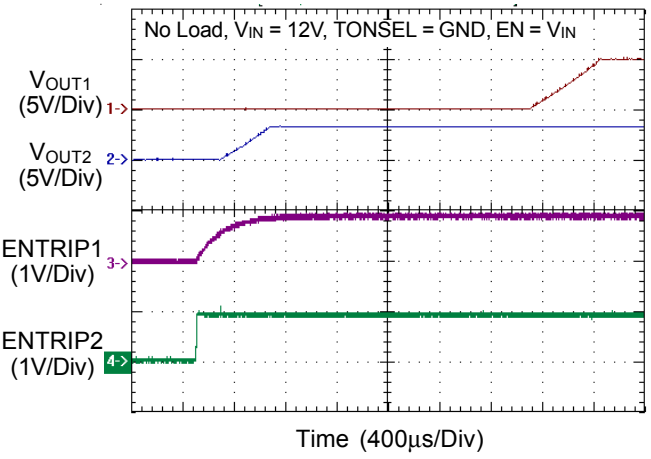
V_{OUT2} Start Up



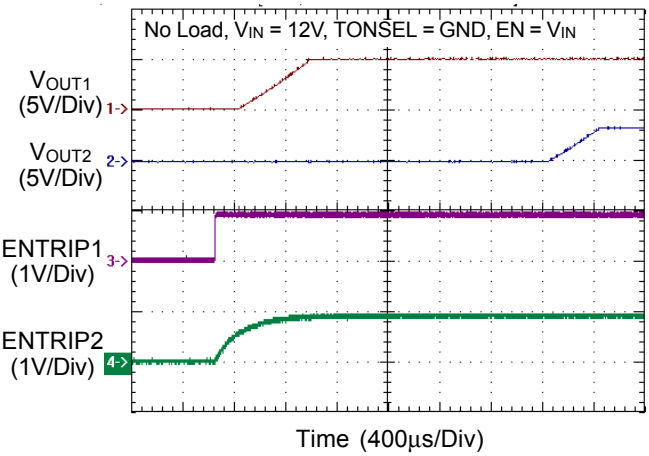
V_{OUT2} Start Up



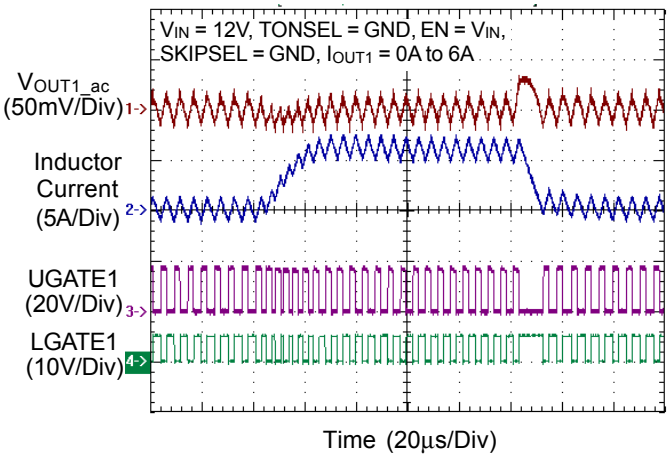
V_{OUT1} Delay Start



V_{OUT2} Delay Start

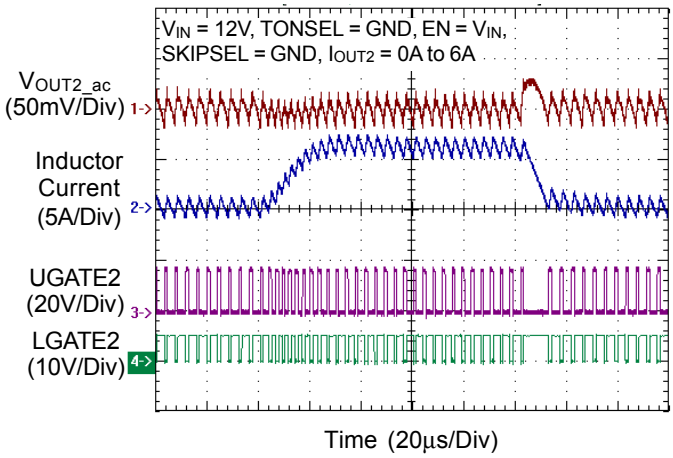


V_{OUT1} PWM Mode Load Transient Response

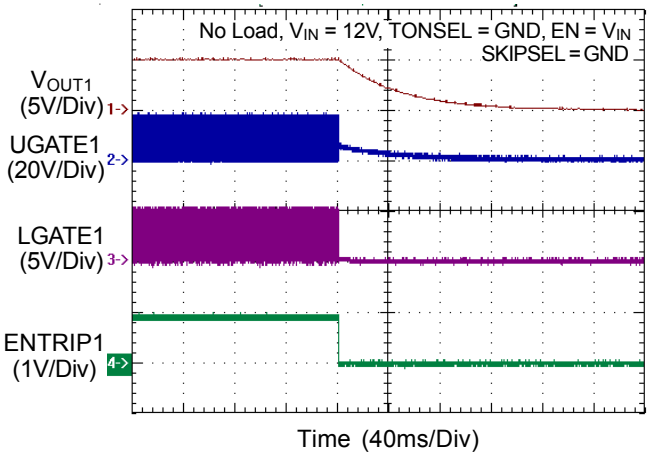


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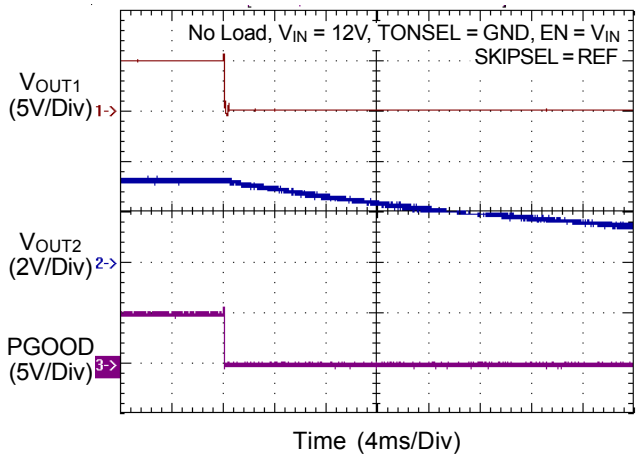
V_{OUT2} PWM Mode Load Transient Response



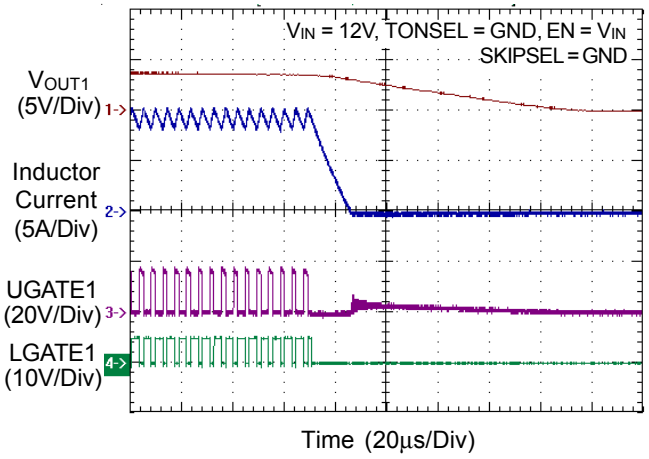
Power Off from ENTRIP1



OVP



UVP



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Application Information

The RT8205A/B/C is a dual, Mach Response™ DRV™ dual ramp valley mode synchronous buck controller. The controller is designed for low-voltage power supplies for notebook computers. Richtek's Mach Response™ technology is specifically designed for providing 100ns "instant-on" response to load steps while maintaining a relatively constant operating frequency and inductor operating point over a wide range of input voltages. The topology circumvents the poor load-transient timing problems of fixed-frequency current-mode PWMs while avoiding the problems caused by widely varying switching frequencies in conventional constant-on-time and constant-off-time PWM schemes. The DRV™ mode PWM modulator is specifically designed to have better noise immunity for such a dual output application. The RT8205A/B/C includes 5V (VREG5) and 3.3V (VREG3) linear regulators. VREG5 linear regulator can step down the battery voltage to supply both internal circuitry and gate drivers. The synchronous-switch gate drivers are directly powered from VREG5. When VOUT1 voltage is above 4.66V, an automatic circuit will switch the power of the device from VREG5 linear regulator from VOUT1.

PWM Operation

The Mach Response™ DRV™ mode controller relies on the output filter capacitor's effective series resistance (ESR) to act as a current-sense resistor, so the output ripple voltage provides the PWM ramp signal. Refer to the RT8205A/B/C's function block diagram, the synchronous high-side MOSFET will be turned on at the beginning of each cycle. After the internal one-shot timer expires, the MOSFET will be turned off. The pulse width of this one shot is determined by the converter's input voltage and the output voltage to keep the frequency fairly constant over the input voltage range. Another one-shot sets a minimum off-time (300ns typ.). The on-time one-shot will be triggered if the error comparator is high, the low-side switch current is below the current-limit threshold, and the minimum off-time one-shot has timed out.

PWM Frequency and On-Time Control

The Mach Response™ control architecture runs with pseudo-constant frequency by feed-forwarding the input and output voltage into the on-time one-shot timer. The high-side switch on-time is inversely proportional to the input voltage as measured by the V_{IN}, and proportional to the output voltage. There are two benefits of a constant switching frequency. The first is the frequency can be selected to avoid noise-sensitive regions such as the 455kHz IF band. The second is the inductor ripple-current operating point remains relatively constant, resulting in easy design methodology and predictable output voltage ripple. The frequency for 3V SMPS is set at 1.25 times higher than the frequency for 5V SMPS. This is done to prevent audio-frequency "beating" between the two sides, which switch asynchronously for each side. The frequencies are set by TONSEL pin connection as Table1. The on-time is given by :

$$\text{On-Time} = K \times (V_{OUT} / V_{IN})$$

where "K" is set by the TONSEL pin connection (Table 1). The on-time guaranteed in the Electrical Characteristics tables are influenced by switching delays in the external high-side power MOSFET. Two external factors that influence switching-frequency accuracy are resistive drops in the two conduction loops (including inductor and PC board resistance) and the dead-time effect. These effects are the largest contributors to the change of frequency with changing load current. The dead-time effect increases the effective on-time, reducing the switching frequency as one or both dead times. It occurs only in PWM mode (SKIPSEL= GND) when the inductor current reverses at light or negative load currents. With reversed inductor current, the inductor's EMF causes PHASEx to go high earlier than normal, extending the on-time by a period equal to the low-to-high dead time. For loads above the critical conduction point, the actual switching frequency is :

$$f = (V_{OUT} + V_{DROP1}) / (t_{ON} \times (V_{IN} + V_{DROP1} - V_{DROP2}))$$

where V_{DROP1} is the sum of the parasitic voltage drops in the inductor discharge path, including synchronous rectifier, inductor, and PC board resistances; V_{DROP2} is the sum of the resistances in the charging path; and t_{ON} is the on-time calculated by the RT8205A/B/C.

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Table 1. TONSEL Connection and Switching Frequency

TON	SMPS 1 K-Factor (µs)	SMPS 1 Frequency (kHz)	SMPS 2 K-Factor (µs)
GND	5	200	4
REF	3.33	300	2.67
VREG5 or VREG3	2.5	400	2

TON	SMPS 2 Frequency (kHz)	Approximate K-Factor Error (%)
GND	250	±10
REF	375	±10
VREG5 or VREG3	500	±10

Operation Mode Selection (SKIPSEL)

The RT8205A/B/C supports three operation modes : Diode-Emulation Mode, Ultrasonic Mode, and Forced-CCM Mode.

Diode-Emulation Mode (SKIPSEL = REF)

In Diode-Emulation mode, The RT8205A/B/C automatically reduces switching frequency at light-load conditions to maintain high efficiency. This reduction of frequency is achieved smoothly and without increase of V_{OUT} ripple or load regulation. As the output current decreases from heavy-load condition, the inductor current is also reduced, and eventually comes to the point that its valley touches zero current, which is the boundary between continuous conduction and discontinuous conduction modes. By emulating the behavior of diodes, the low-side MOSFET allows only partial of negative current when the inductor free-wheeling current reach negative. As the load current is further decreased, it takes longer and longer to discharge the output capacitor to the level that requires the next "ON" cycle. The on-time is kept the same as that in the heavy-load condition. In reverse, when the output current increases from light load to heavy load, the switching frequency increases to the preset value as the inductor current reaches the continuous conduction. The transition load point to the light-load operation can be calculated as follows (Figure 1) :

$$I_{LOAD(SKIP)} \approx \frac{(V_{IN} - V_{OUT})}{2L} \times T_{ON}$$

where Ton is the On-time.

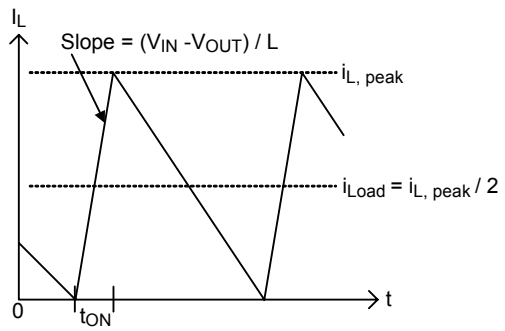


Figure 1. Boundary condition of CCM/DCM

The switching waveforms may appear noisy and asynchronous when light loading causes Diode-Emulation operation, but this is a normal operating condition that results in high light-load efficiency. Trade-offs in PFM noise vs. light-load efficiency are made by varying the inductor value. Generally, low inductor values produce a broader efficiency vs. load curve, while higher values result in higher full-load efficiency (assuming that the coil resistance remains fixed) and less output voltage ripple. Penalties for using higher inductor values include larger physical size and degraded load-transient response (especially at low input-voltage levels).

Ultrasonic Mode (SKIPSEL = VREG5 or VREG3)

Connecting SKIPSEL to VREG5 or VREG3 activates a unique Diode-Emulation mode with a minimum switching frequency of 25kHz. This ultrasonic mode eliminates audio-frequency modulation that would otherwise be present when a lightly loaded controller automatically skips pulses. In ultrasonic mode, the low-side switch gate-driver signal is OR with an internal oscillator (>25kHz). Once the internal oscillator is triggered, the ultrasonic controller pulls LGATEx high, turning on the low-side MOSFET to induce a negative inductor current. After the output voltage across the REF, the controller turns off the low-side MOSFET (LGATEx pulled low) and triggers a constant on-time (UGATEx driven high). When the on-time has expired, the controller re-enables the low-side MOSFET until the controller detects that the inductor current dropped below the zero-crossing threshold.

Forced-CCM Mode (SKIPSEL = GND)

The low-noise, forced-CCM mode (SKIPSEL = GND) disables the zero-crossing comparator, which controls the low-side switch on-time. This causes the low-side gate-

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driver waveform to become the complement of the high-side gate-driver waveform. This in turn causes the inductor current to reverse at light loads as the PWM loop to maintain a duty ratio of V_{OUT}/V_{IN}. The benefit of forced-CCM mode is to keep the switching frequency fairly constant, but it comes at a cost : The no-load battery current can be 10mA to 40mA, depending on the external MOSFETs.

Reference and linear Regulators (REF, VREGx)

The 2V reference (REF) is accurate within ±1% over temperature, making REF useful as a precision system reference. Bypass REF to GND with a 0.22uF (min) capacitor. REF can supply up to 50uA for external loads. Loading REF reduces the VOUTx output voltage slightly because of the reference load-regulation error.

VREG5 regulator supplies total of 70mA for internal and external loads, including MOSFET gate driver and PWM controller. VREG3 regulator supplies up to 70mA for external loads. Bypass VREG5 and VREG3 with a 4.7uF (min) capacitor; use an additional 1uF per 5mA of internal and external load.

When the 5V main output voltage is above the VREG5 switchover threshold, an internal 1.5Ω N-Channel MOSFET switch connects VOUT1 to VREG5 while simultaneously shutting down the VREG5 linear regulator. Similarly, when the 3.3V main output voltage is above the VREG3 switchover threshold, an internal 1.5Ω N-Channel MOSFET switch connects VOUT2 to VREG3 while simultaneously shutting down the VREG3 linear regulator. It can decrease the power dissipation from the same battery, because the converted efficiency of SMPS is better than the converted efficiency of linear regulator.

Current-Limit Setting (ENTRIPx)

The RT8205A/B/C has cycle-by-cycle current limiting control. The current-limit circuit employs a unique "valley" current sensing algorithm. If the magnitude of the current-sense signal at PHASEx is above the current-limit threshold, the PWM is not allowed to initiate a new cycle (Figure 2). The actual peak current is greater than the current-limit threshold by an amount equal to the inductor ripple current. Therefore, the exact current-limit characteristic and maximum load capability are a function of the sense resistance, inductor value, and battery and output voltage.

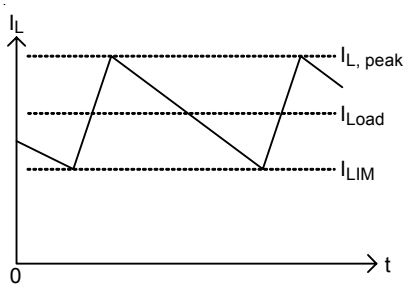


Figure 2. "valley" Current-Limit

The RT8205A/B/C uses the on-resistance of the synchronous rectifier as the current-sense element. Use the worse-case maximum value for $R_{DS(ON)}$ from the MOSFET datasheet, and add a margin of 0.5%/°C for the rise in $R_{DS(ON)}$ with temperature.

The R_{ILIM} resistor between the ENTRIPx pin and GND sets the over current threshold. The resistor R_{ILIM} is connected to a 10uA current source from ENTRIPx. When the voltage drop across the sense resistor or low-side MOSFET equals 1/10 the voltage across the R_{ILIM} resistor, positive current limit will be activated. The high-side MOSFET will not be turned on until the voltage drop across the MOSFET falls below 1/10 the voltage across the R_{ILIM} resistor.

Choose a current limit resistor by following equation :

$V_{ILIM} = (R_{ILIM} \times 10uA) / 10 = I_{ILIM} \times R_{DS(ON)}$

$R_{ILIM} = (I_{ILIM} \times R_{DS(ON)}) \times 10 / 10uA$

Carefully observe the PC board layout guidelines to ensure that noise and DC errors do not corrupt the current-sense signal at PHASEx and GND. Mount or place the IC close to the low-side MOSFET.

Charge Pump (LG1_CP or SECFB)

The external 14V charge pump is driven by LGATE1 (Figure 3 and Figure 4). When LGATE1 is low, the C1 will be charged by D1 from VOUT1. C1 voltage is equal to V_{OUT1} minus a diode drop. When LGATE1 transitions to high, the charges from C1 will transfer to C2 through D2 and charge it to V_{LGATE1} plus VC1. As LGATE1 transitions low on the next cycle, C2 will charge C3 to its voltage minus a diode drop through D3. Finally, C3 charges C4 through

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D4 when LGATE1 switched to high. So, V_{CP} voltage is :

$V_{CP} = V_{OUT1} + 2 \times V_{LGATE1} - 4 \times V_D$

Where V_{LGATE1} is the peak voltage of LGATE1 driver and is equal to the VREG5; V_D is the forward diode dropped across the Schottky.

LG1_CP in the RT8205B (Figure 3) can be used as clock signal for charge pump circuit to generate approximately 14V DC voltage and the clock driver uses VOUT1 as its power supply, SECFB in the RT8205C is used to monitor the charge pump through resistive divider (Figure 4). In an event when SECFB dropped below 2V, the detection circuit forces the high-side MOSFET off and the low-side MOSFET on for 300ns to allow CP to recharge and SECFB rise above 2V. In the event of an overload on CP where SECFB can not reach more than 2V, the monitor will be cancelled. Special care should be taken to ensure enough normal voltage ripple on each cycle as to prevent CP shut-down.

The SECFB pin has ~17mV of hysteresis, so the ripple should be enough to bring the SECFB voltage above the threshold by ~3x the hysteresis, or (2V + 3 x 17mV) = 2.051V. Reducing the CP decoupling capacitor and placing a small ceramic capacitor (10 pF to 47pF) (C_F of Figure 4) in parallel with the upper leg of the SECFB resistor feedback network (R_{CP1} of Figure 4) will also increase the robustness of the charge pump.

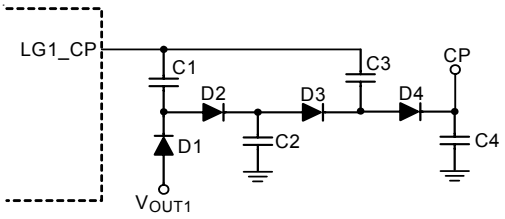


Figure 3. Connect to LG1_CP

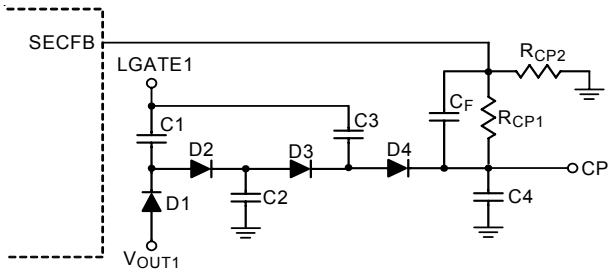


Figure 4. Connect to SECFB

MOSFET Gate Driver (UGATEx, LGATEx)

The high-side driver is designed to drive high-current, low $R_{DS(ON)}$ N-MOSFET(s). When configured as a floating driver, 5-V bias voltage is delivered from VREG5 supply. The average drive current is also calculated by the gate charge at V_{GS} = 5 V times switching frequency. The instantaneous drive current is supplied by the flying capacitor between BOOTx and PHASEx pins. A dead time to prevent shoot through is internally generated between high-side MOSFET off to low-side MOSFET on, and low-side MOSFET off to high-side MOSFET on.

The low-side driver is designed to drive high current low $R_{DS(ON)}$ N-MOSFET(s). The internal pull-down transistor that drives LGATEx low is robust, with a 0.6Ω typical on-resistance. A 5V bias voltage is delivered from VREG5 supply. The instantaneous drive current is supplied by an input capacitor connected between VREG5 and GND.

For high-current applications, some combinations of high- and low-side MOSFETs might be encountered that will cause excessive gate-drain coupling, which can lead to efficiency-killing, EMI-producing shoot-through currents. This is often remedied by adding a resistor in series with BOOTx, which increases the turn-on time of the high-side MOSFET without degrading the turn-off time (Figure 5).

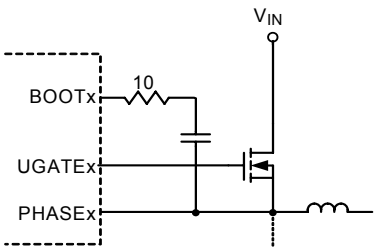


Figure 5. Reducing the UGATEx Rise Time

Soft-Start

A build-in soft-start is used to prevent surge current from power supply input after ENTRIPx is enabled. The typical soft-start duration is 2ms period. Furthermore, the maximum allowed current limit is segmented in 5 steps: 20%, 40%, 60%, 80% and 100% during the 2ms period.

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UVLO Protection

The RT8205A/B/C has VREG5 under voltage lock out protection (UVLO). When the VREG5 voltage is lower than 4.2V (typ.) and the VREG3 voltage is lower than 2.5V (typ.), both switch power supplies are also shut off. This is non-latch protection.

Power-Good Output (PGOOD)

The PGOOD is an open-drain type output and requires a pull-up resistor. PGOOD is actively held low in soft-start, standby, and shutdown. It is released when both outputs voltage above than 92.5% of nominal regulation point. The PGOOD goes low if either output turns off or is 10% below its nominal regulator point.

Output Over Voltage Protection (OVP)

The output voltage can be continuously monitored for over voltage. When over voltage protection is enabled, if the output voltage exceeded 11% of its set voltage threshold, the over voltage protection is triggered and the LGATEx low-side gate drivers are forced high. This activates the low-side MOSFET switch, which rapidly discharges the output capacitor and pulls the input voltage downward.

RT8205A/B/C is latched once OVP is triggered and can only be released by EN power-on reset. There is 10us delay built into the over voltage protection circuit to prevent false transition.

Note that LGATEx latching high causes the output voltage to dip slightly negative when energy has been previously stored in the LC tank circuit. For loads that cannot tolerate a negative voltage, place a power Schottky diode across the output to act as a reverse polarity clamp.

If the over voltage condition is caused by a short in high-side switch, turning the low-side MOSFET on 100% creates an electrical short between the battery and GND, blowing the fuse and disconnecting the battery from the output.

Output Under voltage Protection (UVP)

The output voltage can be continuously monitored for under voltage. When under voltage protection is enabled, if the output is less than 70% of its set voltage threshold, under voltage protection is triggered, then both UGATEx and LGATEx gate drivers are forced low while entering soft-discharge mode. During soft-start, the UVP will be blanked around 3ms.

Thermal Protection

The RT8205A/B/C have thermal shutdown to prevent the overheat damage. Thermal shutdown occurs when the die temperature exceeds +150°C. All internal circuitry shuts down during thermal shutdown. The RT8205A/B/C triggers thermal shutdown if VREGx is not supplied from VOUTx, while input voltage on VIN and drawing current form VREGx are too high. Even if VREGx is supplied from VOUTx, overloading the VREGx causes large power dissipation on automatic switches, which may result in thermal shutdown.

Discharge Mode (Soft-Discharge)

When ENTRIPx is low and a transition to standby or shutdown mode occurs, or the output under voltage fault latch is set, the outputs discharge mode will be triggered. During discharge mode, there is one path to discharge the outputs capacitor residual charge. That is output capacitor discharge to GND through an internal switch.

Shutdown Mode

The RT8205A/B/C SMPS1, SMPS2, VREG3 and VREG5 have independent enabling control. Drive EN, ENTRIP1 and ENTRIP2 below the precise input falling-edge trip level to place the RT8205A/B/C in its low-power shutdown state. The RT8205A/B/C consumes only 20uA of input current while in shutdown.

Power-Up Sequencing and On/Off Controls (ENTRIPx)

ENTRIP1 and ENTRIP2 control SMPS power-up sequencing. When the RT8205A/B/C applies in the single channel mode, ENTRIP1 or ENTRIP2 enables the respective outputs when ENTRIPx voltage rising above 0.4V.

If both of ENTRIP1 and ENTRIP2 become higher than the enable threshold voltage at a different time (without 60us), one can force the latter one output starts after the former one regulates.

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Output Voltage Setting (FBx)

Connect FBx directly to GND or VREG5 to enable the fixed, SMPS output voltages (3.3V and 5V). Connect a resistor voltage-divider at the FBx between the VOUTx and GND to adjust the respective output voltage between 2V and 5.5V (Figure 6). Choose R2 to be approximately 10kΩ, and solve for R1 using the equation :

$$V_{OUTx} = V_{FBx} \times \left[1 + \left(\frac{R1}{R2}\right)\right]$$

where V_{FBx} is 2V (typ.).

VREG5 connects to VOUT1 through an internal switch only when VOUT1 is above the VREG5 automatic switch threshold (4.66V). VREG3 connects to VOUT2 through an internal switch only when VOUT2 is above the VREG3 automatic switch threshold (3.06V). This is the most effective way when the fixed output voltages are used. Once VREGx is supplied from VOUTx, the internal linear regulator turns off. This reduces internal power dissipation and improves efficiency when the VREGx is powered with a high input voltage.

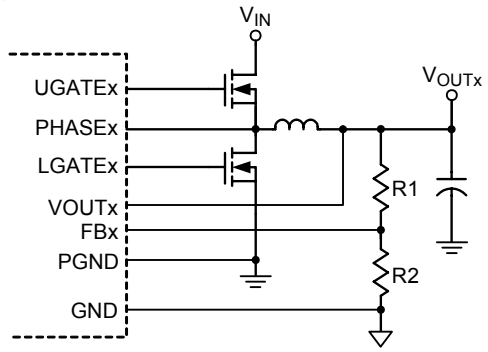


Figure 6. Setting VOUTx with a Resistor-Divider

Output Inductor Selection

The switching frequency (on-time) and operating point (% ripple or L_{IR}) determine the inductor value as shown as follows :

$$L = \frac{T_{ON} \times (V_{IN} - V_{OUTx})}{L_{IR} \times I_{LOAD(MAX)}}$$

where L_{IR} is the ratio of the peak to peak ripple current to the average inductor current.

Find a low-loss inductor having the lowest possible DC resistance that fits in the allotted dimensions. Ferrite cores are often the best choice, although powdered iron is inexpensive and can work well at 200kHz. The core must be large enough not to saturate at the peak inductor current (I_{PEAK}) :

$$I_{PEAK} = I_{LOAD(MAX)} + [(L_{IR} / 2) \times I_{LOAD(MAX)}]$$

This inductor ripple current also impacts transient-response performance, especially at low VIN – VOUTx differences. Low inductor values allow the inductor current to slew faster, replenishing charge removed from the output filter capacitors by a sudden load step. The peak amplitude of the output transient V_{SAG} is also a function of the output transient. The V_{SAG} also features a function of the maximum duty factor, which can be calculated from the on-time and minimum off-time :

$$V_{SAG} = \frac{(\Delta I_{LOAD})^2 \times L \times \left(K \frac{V_{OUTx}}{V_{IN}} + T_{OFF(MIN)}\right)}{2 \times C_{OUT} \times V_{OUTx} \times \left[K\left(\frac{V_{IN} - V_{OUTx}}{V_{IN}}\right) - T_{OFF(MIN)}\right]}$$

Where minimum off-time ($T_{OFF(MIN)}$) = 300ns (typ.) and K is from Table 1.

Output Capacitor Selection

The output filter capacitor must have low enough ESR to meet output ripple and load-transient requirements, yet have high enough ESR to satisfy stability requirements. Also, the capacitance value must be high enough to absorb the inductor energy going from a full-load to no-load condition without tripping the OVP circuit.

For CPU core voltage converters and other applications where the output is subject to violent load transients, the output capacitor's size depends on how much ESR is needed to prevent the output from dipping too low under a load transient. Ignoring the sag due to finite capacitance :

$$ESR \leq \frac{V_{P-P}}{I_{LOAD(MAX)}}$$

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In non-CPU applications, the output capacitor's size depends on how much ESR is needed to maintain an acceptable level of output voltage ripple :

$$ESR \leq \frac{V_{P-P}}{L_{IR} \times I_{LOAD(MAX)}}$$

where V_{P-P} is the peak-to-peak output voltage ripple.

Organic semiconductor capacitor(s) or specialty polymer capacitor(s) are recommended.

For low input-to-output voltage differentials (VIN / VOUTx < 2), additional output capacitance is required to maintain stability and good efficiency in ultrasonic mode.

The amount of overshoot due to stored inductor energy can be calculated as :

$$V_{SOAR} \leq \frac{(I_{PEAK})^2 \times L}{2 \times C_{OUT} \times V_{OUTx}}$$

where I_{PEAK} is the peak inductor current.

Although Mach Response™ DRV™ dual ramp valley mode provides many advantages such as ease-of-use, minimum external component configuration, and extremely short response time, due to not employing an error amplifier in the loop, a sufficient feedback signal needs to be provided by an external circuit to reduce the jitter level. The required signal level is approximately 15mV at the comparing point. This generates V_{Ripple} = (V_{OUT} / 2) x 15mV at the output node. The output capacitor ESR should meet this requirement.

Output Capacitor Stability

Stability is determined by the value of the ESR zero relative to the switching frequency. The point of instability is given by the following equation :

$$f_{ESR} = \frac{1}{2 \times \pi \times ESR \times C_{OUT}} \leq \frac{f_{SW}}{4}$$

Do not put high-value ceramic capacitors directly across the outputs without taking precautions to ensure stability. Large ceramic capacitors can have a high- ESR zero frequency and cause erratic, unstable operation. However, it is easy to add enough series resistance by placing the capacitors a couple of inches downstream from the inductor and connecting VOUTx or the FBx divider close to the inductor.

Unstable operation manifests itself in two related and distinctly different ways: double-pulsing and feedback loop instability.

Double-pulsing occurs due to noise on the output or because the ESR is so low that there is not enough voltage ramp in the output voltage signal. This “fools” the error comparator into triggering a new cycle immediately after the 300ns minimum off-time period has expired. Double-pulsing is more annoying than harmful, resulting in nothing worse than increased output ripple. However, it may indicate the possible presence of loop instability, which is caused by insufficient ESR.

Loop instability can result in oscillations at the output after line or load perturbations that can trip the overvoltage protection latch or cause the output voltage to fall below the tolerance limit.

The easiest method for checking stability is to apply a very fast zero-to-max load transient and carefully observe the output-voltage-ripple envelope for overshoot and ringing. It helps to simultaneously monitor the inductor current with an AC current probe. Do not allow more than one cycle of ringing after the initial step-response under- or overshoot.

Thermal Considerations

For continuous operation, do not exceed absolute maximum operation junction temperature. The maximum power dissipation depends on the thermal resistance of IC package, PCB layout, the rate of surroundings airflow and temperature difference between junction to ambient. The maximum power dissipation can be calculated by following formula :

$$P_{D(MAX)} = (T_{J(MAX)} - T_A) / \theta_{JA}$$

Where $T_{J(MAX)}$ is the maximum operation junction temperature, T_A is the ambient temperature and the θ_{JA} is the junction to ambient thermal resistance.

For recommended operating conditions specification, the maximum junction temperature is 125°C. The junction to ambient thermal resistance θ_{JA} is layout dependent. For WQFN-24L 4x4 packages, the thermal resistance θ_{JA} is 52°C/W on the standard JEDEC 51-7 four layers thermal

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test board. The maximum power dissipation at T_A = 25°C can be calculated by following formula :

$P_{D(MAX)}$ = (125°C − 25°C) / (52°C/W) = 1.923W for WQFN-24L 4x4 packages

The maximum power dissipation depends on operating ambient temperature for fixed $T_{J(MAX)}$ and thermal resistance θ_{JA}. The Figure 7 of derating curves allows the designer to see the effect of rising ambient temperature on the maximum power allowed.

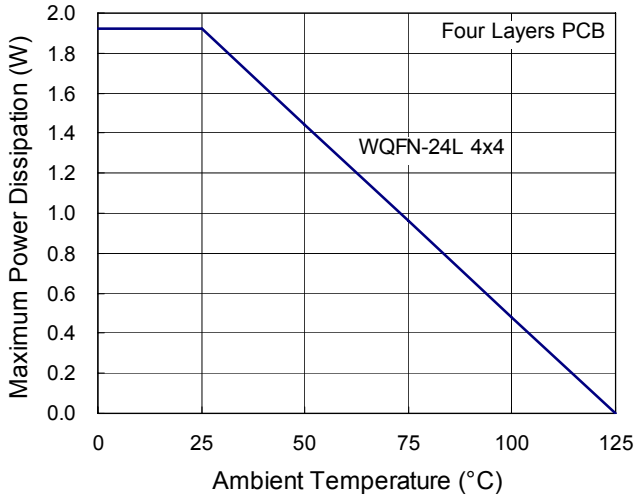


Figure 7. Derating Curve of Maximum Power Dissipation

Layout Considerations

Layout is very important in high frequency switching converter design. If the IC is designed improperly, the PCB could radiate excessive noise and contribute to the converter instability. Certain points must be considered before starting a layout using the RT8205A/B/C.

- Place the filter capacitor close to the IC, within 12 mm (0.5 inch) if possible.
- Keep current limit setting network as close as possible to the IC. Routing of the network should avoid coupling to high-voltage switching node.
- Connections from the drivers to the respective gate of the high-side or the low-side MOSFET should be as short as possible to reduce stray inductance. Use 0.65-mm (25 mils) or wider trace.
- All sensitive analog traces and components such as VOUTx, FBx, GND, ENTRIPx, PGOOD, and TONSEL should be placed away from high-voltage switching nodes such as PHASEx, LGATEx, UGATEx, or BOOTx nodes to avoid coupling. Use internal layer(s) as ground plane(s) and shield the feedback trace from power traces and components.
- Gather ground terminal of VIN capacitor(s), VOUTx capacitor(s), and source of low-side MOSFETs as close as possible. PCB trace defined as PHASEx node, which connects to source of high-side MOSFET, drain of low-side MOSFET and high-voltage side of the inductor, should be as short and wide as possible.

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Table 2. Operation Mode Truth Table

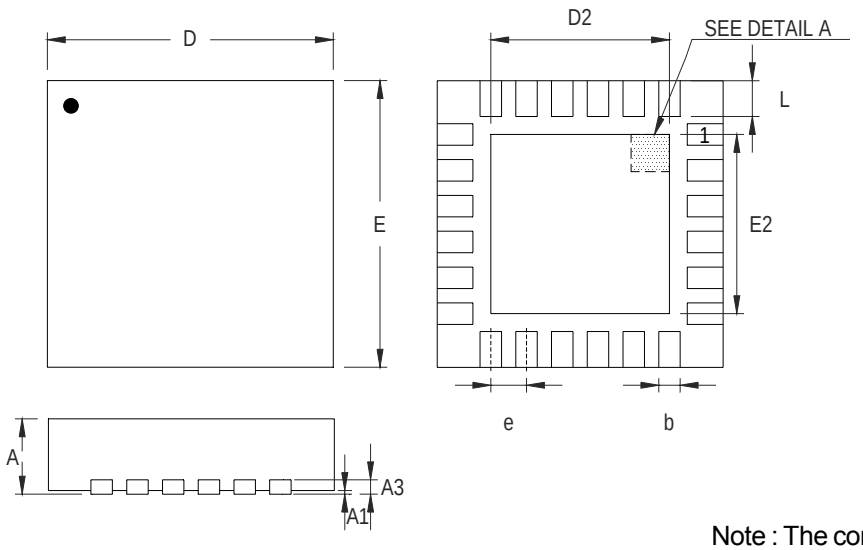
Mode	Condition	Comment
Power-UP	VREGx < UVLO threshold	Transitions to discharge mode after a VIN POR and after REF becomes valid. VREG5, VREG3, and REF remain active.
RUN	EN = high, VOUT1 or VOUT2 enabled	Normal Operation.
Over Voltage Protection	Either output > 111% of the nominal level.	LGATEx is forced high. VREG3, VREG5 active. Exited by VIN POR or by toggling EN, ENTRIPx
Under Voltage Protection	Either output < 70% of the nominal level after 3ms time-out expires and output is enabled	Both UGATEx and LGATEx are forced low and enter discharge mode. VREG3, VREG5 active. Exited by VIN POR or by toggling EN, ENTRIPx
Discharge	Either SMPS output is still high in either standby mode or shutdown mode	During discharge mode, there is one path to discharge the outputs capacitor residual charge. That is output capacitor discharge to GND through an internal switch.
Standby	ENTRIPx < startup threshold, EN = high.	VREG3, VREG5 active.
Shutdown	EN = low	All circuitry off.
Thermal Shutdown	TJ > +150°C	All circuitry off. Exit by VIN POR or by toggling EN, ENTRIPx.

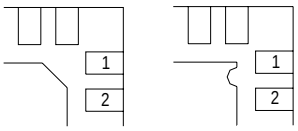
Table 3. Power-Up Sequencing

EN (V)	ENTRIP1 (V)	ENTRIP2 (V)	VREG5	VREG3	SMPS1	SMPS2
Low	X	X	Off	Off	Off	Off
“>1V” => High	Low	Low	On (after REF powers up)	On (after REF powers up)	Off	Off
“>1V” => High	Low	High	On (after REF powers up)	On (after REF powers up)	Off	On
“>1V” => High	High (after ENTRIP2 is high without 60us)	High	On (after REF powers up)	On (after REF powers up)	On (after SMPS2 on)	On
“>1V” => High	High	Low	On (after REF powers up)	On (after REF powers up)	On	Off
“>1V” => High	High	High (after ENTRIP1 is high without 60us)	On (after REF powers up)	On (after REF powers up)	ON	On (after SMPS1 on)
“>1V” => High	High	High	On (after REF powers up)	On (after REF powers up)	On	On

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Outline Dimension





DETAIL A

Pin #1 ID and Tie Bar Mark Options

Note : The configuration of the Pin #1 identifier is optional, but must be located within the zone indicated.

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A3	0.175	0.250	0.007	0.010
b	0.180	0.300	0.007	0.012
D	3.950	4.050	0.156	0.159
D2	2.300	2.750	0.091	0.108
E	3.950	4.050	0.156	0.159
E2	2.300	2.750	0.091	0.108
e	0.500		0.020	
L	0.350	0.450	0.014	0.018

W-Type 24L QFN 4x4 Package

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